Noise and Reliability in Advanced Bipolar Technologies

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Outline

- **Introduction:**
  - **Limitations in existing noise models.**
  - **Importance and motivation of research.**
- **Noise in polysilicon emitter bipolar transistors:**
  - **Experimental setup.**
  - **S_{IB} modeling:**
    - **noise mechanisms, effect of bias, geometry and IFO.**
  - **S_{IC} modeling:**
    - **noise mechanisms, effect of bias and IFO.**
  - **S_{Vr} modeling:**
    - **Collector-emitter measurement setup, effect of bias and IFO.**
  - **Computer codes.**
- **Noise in SiGe heterojunction bipolar transistors:**
  - **Dominant noise source.**
  - **Effect of selective collector implant.**
  - **Effect of higher extrinsic base implant.**
  - **Effect of SiGe epi-SiGe poly interface.**
  - **Effect of emitter-poly overlap.**
  - **Physical origin and modeling of $S_{IB.}$**
- **Conclusion**

Current BJT low-frequency noise models

- **Gummel-Poon:** $$I_{BN}^2 = \frac{KF \cdot I_B^{AF}}{f^{EF}} \cdot \Delta f$$

- **VBIC – Flicker noise due to IBE, IBEP**

- **MEXTRAM:** $$\overline{iN_B^2} = \frac{MULT}{f}\left[KFN\left(\frac{|I_{B2}|}{MULT}\right)^2 + KF\left(\frac{|I_{B1}|}{MULT}\right)^2\right] \cdot \Delta f$$

- **MODELLA:** $$\overline{iN_B^2} = \frac{KF \cdot MULT^{1-AF}\,|I_{RE} + I_{LE}|^{AF}}{f} \cdot \Delta f$$

Importance and motivation

Limitations in existing noise models:

- Only one single noise source in base current: $S_{IB}=KF.I_B^{AF}$.
  - Noise in base current dominant only for higher base series resistance.
  - Does not include any geometry, temperature or process parameter.
- Noise in collector current and internal resistances are neglected.
  - Noise in collector current contributes at lower base series resistance.
  - Noise from internal resistance contributes at higher bias current.

Research goal:

- To model all possible noise sources in advanced bipolar transistors:
  - Noise in base current, collector current and internal resistances.
- Developing physics based scalable equations for the noise sources:
  - Incorporating geometry, temperature and process dependant parameters.
- Writing computer source code for device and circuit analysis CAD tools to incorporate all possible noise sources in BJT.

Advanced bipolar technologies under investigation

- **Polysilicon emitter bipolar transistors:**
  - **2nd generation BiCMOS technology, Texas Instruments Inc.**
    - **NPN and PNP transistors.**
    - **Variable size, variable IFO thickness.**
- **SiGe heterojunction bipolar transistors:**
  - **1st generation BiCMOS technology, National Semiconductor Corporation.**
    - **NPN transistors.**
    - **Variable size, variable design rules.**
    - **Variable doping in base and collector.**

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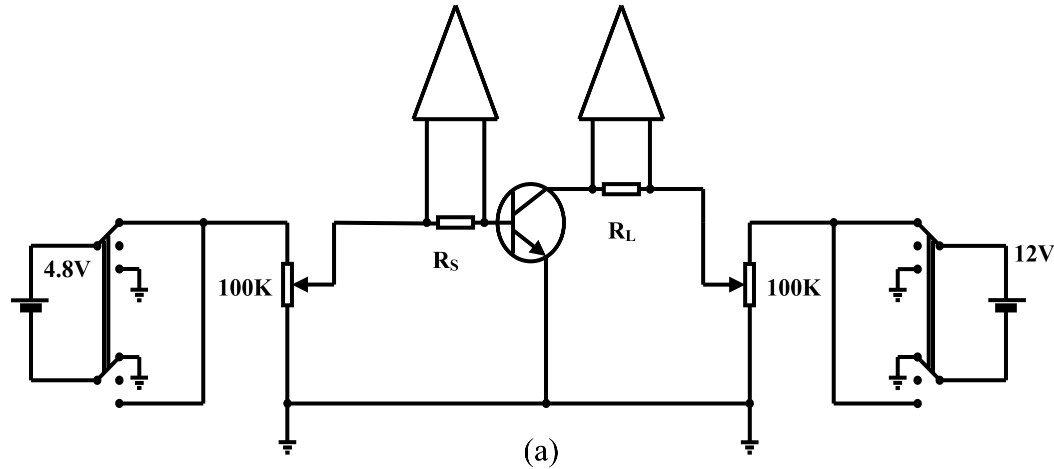
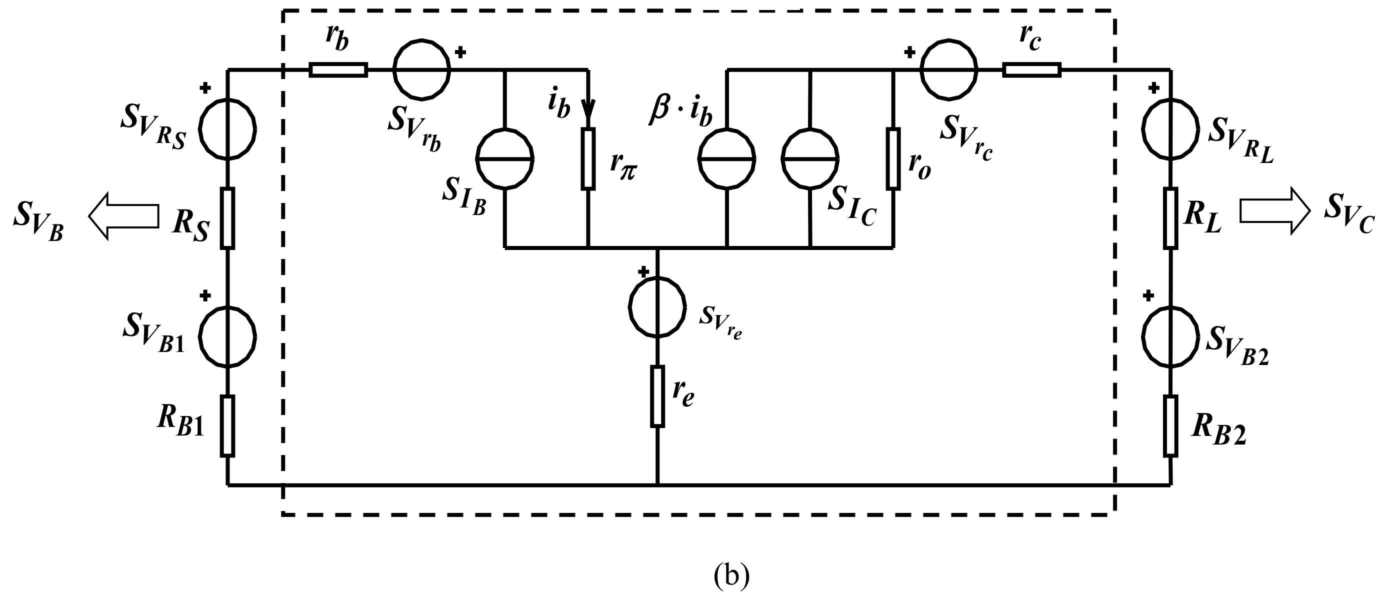
Collector-base measurement setup



(a)



(b)

Collector-base measurement

$$S_{V_C} = x \cdot S_{V_r} + y \cdot S_{I_B} + z \cdot S_{I_C}$$

$$S_{V_B} = u \cdot S_{V_r} + v \cdot S_{I_B} + w \cdot S_{I_C}$$

$$\gamma^2 = \frac{\left|S_{V_{BC}}\right|^2}{S_{V_B} \cdot S_{V_C}}$$

$$S_{V_r} = S_{V_{r_e}} + S_{V_{r_b}}$$

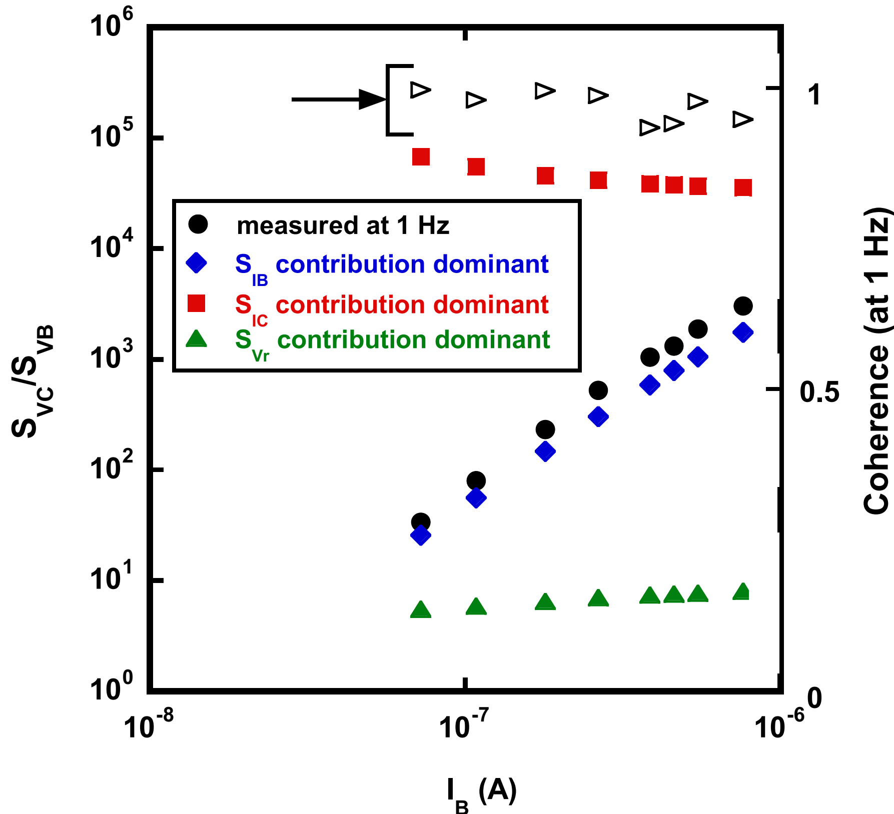
for unity coherence:

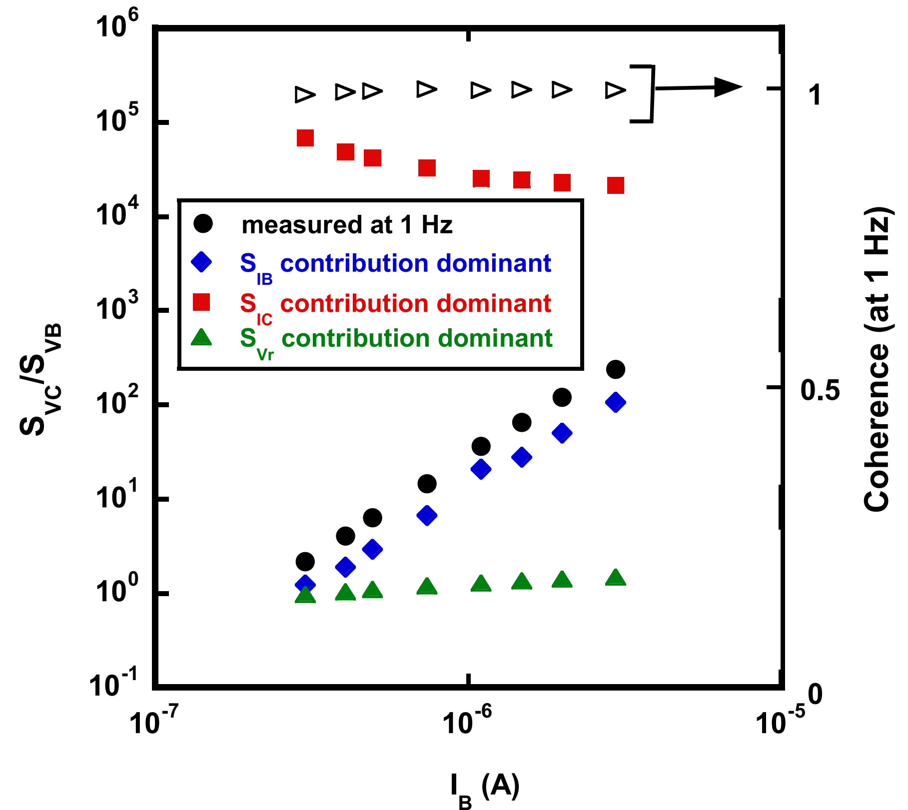
If S_{V_r} **has the dominant contribution,** $\frac{S_{V_C}}{S_{V_B}} \approx \frac{x}{u}$

If S_{I_B} **has the dominant contribution,** $\frac{S_{V_C}}{S_{V_B}} \approx \frac{y}{v}$

If S_{I_C} **has the dominant contribution,** $\frac{S_{V_C}}{S_{V_B}} \approx \frac{z}{w}$

Dominant noise source





- **Calculated S_{VC}/S_{VB} considering S_{IB} contribution dominant closely matches experimental S_{VC}/S_{VB}; SIB contribution dominant.**

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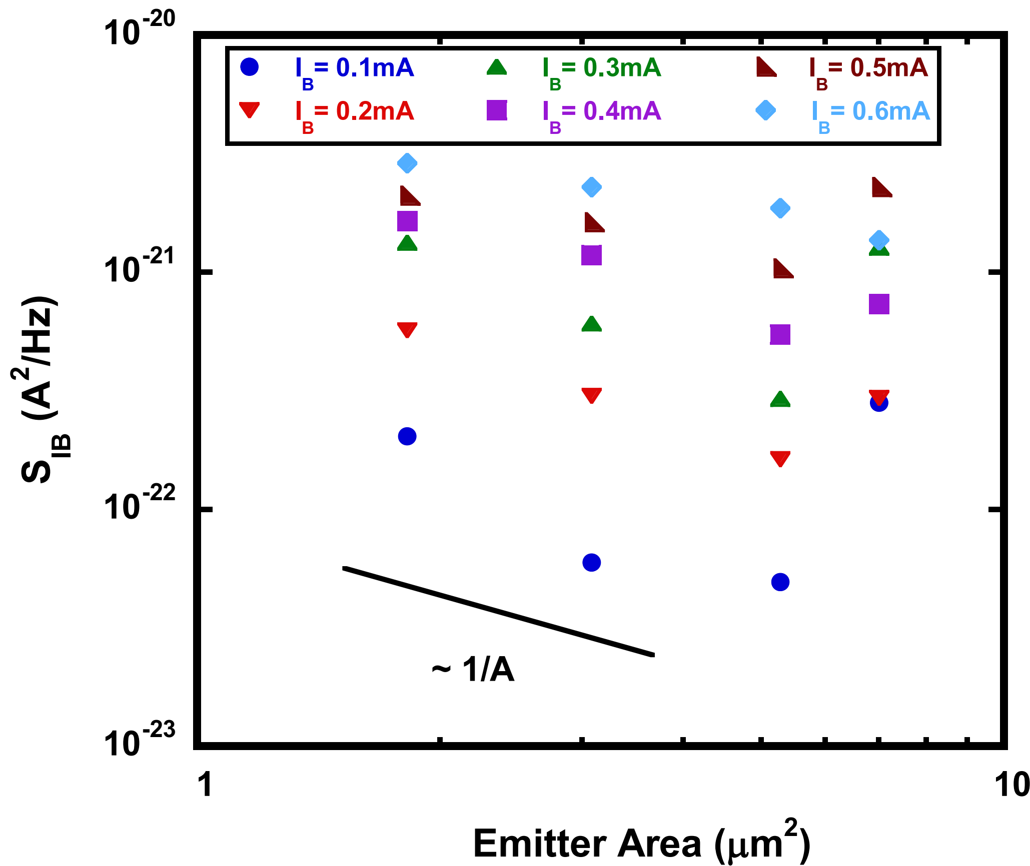
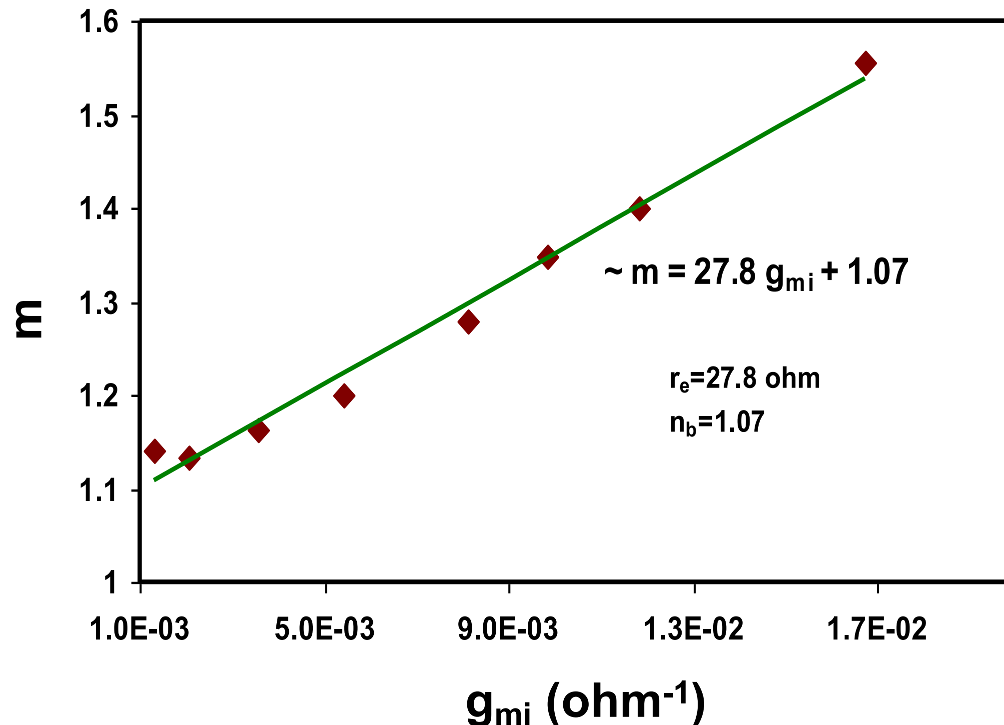
Area dependence of S_{IB} in NPN transistors



[Darby Lan]

Noise source homogeneously distributed underneath the emitter.

Internal emitter resistance and ideality factor of base current



$$m = r_e \cdot g_{mi} + n_b$$

$$m = \frac{\beta \cdot R_L}{r_{\pi i}} \sqrt{\frac{S_{V_B}}{S_{V_C}}}$$

$$r_{\pi i} = \frac{kT}{qI_B}$$

$$g_{mi} = \frac{\beta}{r_{\pi i}}$$

Physical origin of S_{IB}

- Base current dependence

  - $S_{I_{B_{diff}}} \propto I_{B_{diff}}$ → diffusion fluctuation in emitter.

  - $S_{I_{B_{tun}}} \propto I_{B_{tun}}^2$ → tunneling fluctuation in IFO.

  - $S_{I_{B_{rec}}} \propto I_{B_{rec}}^2$ → recombination fluctuation in emitter-base space charge region. → recombination fluctuation at spacer oxide interface.

- Emitter perimeter dependence
  - Noise source distributed homogeneously around the emitter.
  - Recombination fluctuation at the spacer oxide interface.
- Emitter area dependence
  - Noise source distributed homogeneously underneath the emitter.
  - Diffusion fluctuation in emitter or tunneling fluctuation in IFO.

Physical origin of S_{IB} (cont.)

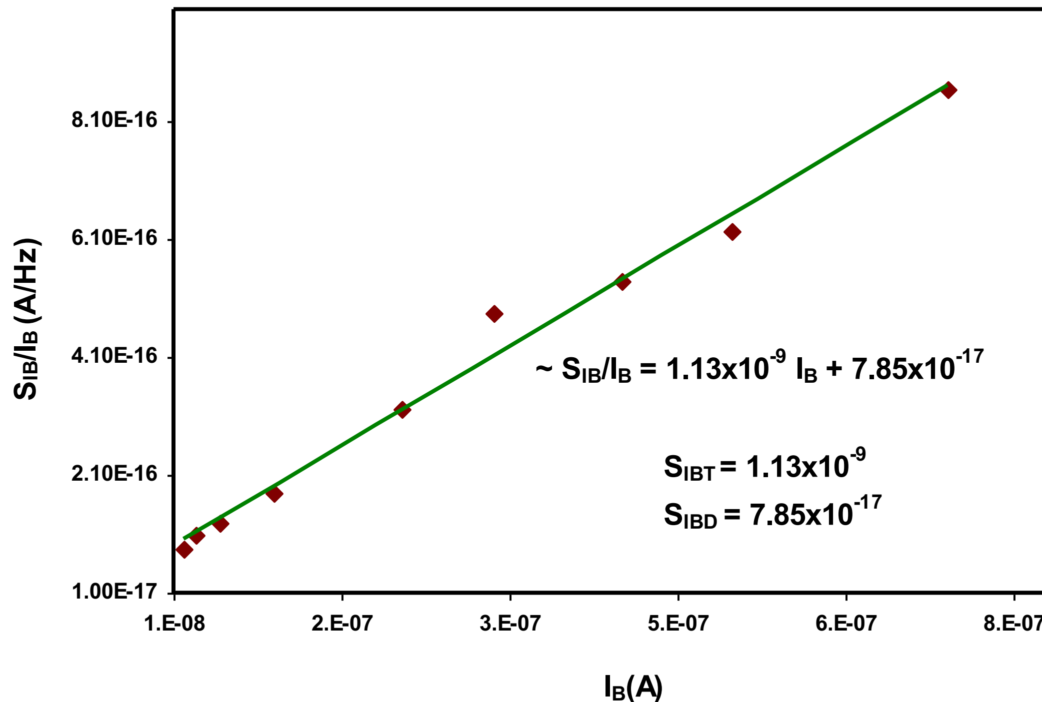
$$S_{I_B} = S_{I_{B_{diff}}} + S_{I_{B_{tun}}} + S_{I_{B_{rec}}}$$

- **Unity ideality factor of** I_B → **negligible** $I_{B_{rec}}$.

  → **negligible** $S_{I_{B_{rec}}}$.

$$S_{I_B} \approx S_{I_{B_{diff}}} + S_{I_{B_{tun}}}$$

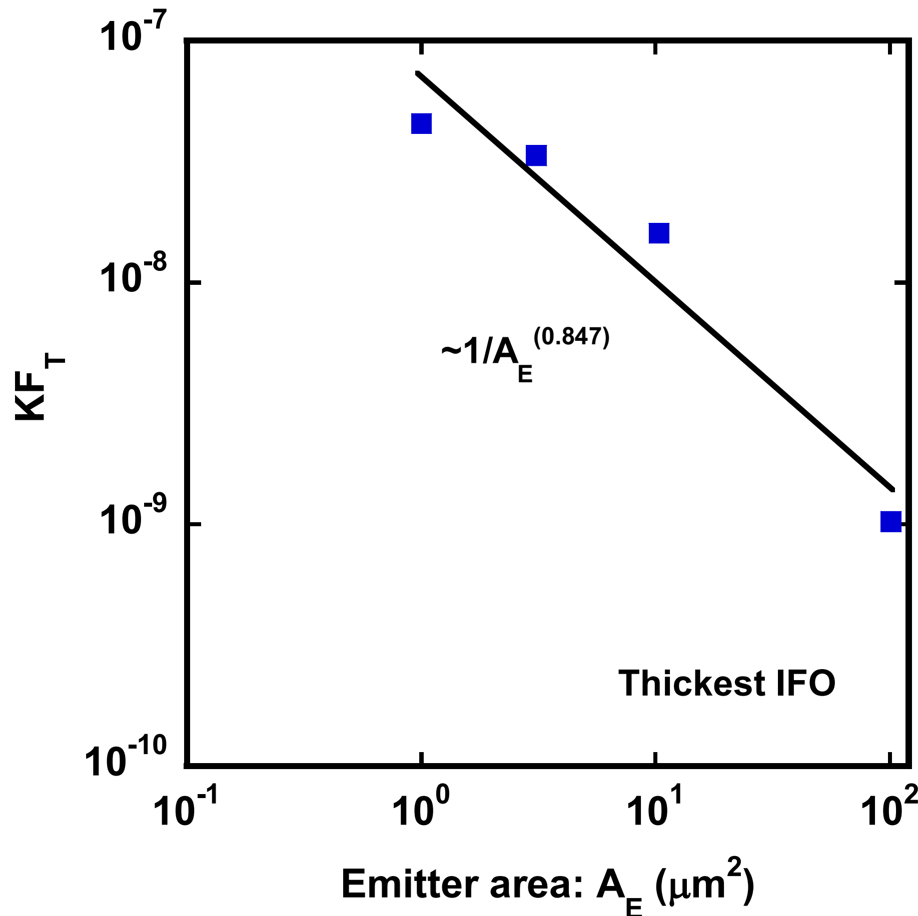
Diffusion and tunneling fluctuation component of S_{IB}



$$S_{I_B} = S_{I_{B_D}} + S_{I_{B_T}}$$
$$= KF_D \cdot I_B + KF_T \cdot I_B^2$$

$$\frac{S_{I_B}}{I_B} = KF_D + KF_T \cdot I_B$$

Area dependence of tunneling fluctuation of S_{IB} in PNP transistors



Tunneling-fluctuation source homogeneously distributed underneath the emitter.

Smaller device-dimension severely affected by lateral diffusion and mask undercut; effective emitter area considered.

Diffusion fluctuation in S_{IB}

$$\frac{S_{I_{B_D}}}{I_B} = \frac{\dfrac{\alpha_m q}{D_m f}\ln\left[\dfrac{p(0)}{p(x_1)}\right] + \dfrac{\alpha_p q}{D_p f}\ln\left[\dfrac{p(x_2)}{p(x_3)}\right]}{\left(\dfrac{W_m}{D_m} + \dfrac{W_p}{D_p} + \dfrac{1}{s_{ox}} + \dfrac{1}{s_m}\right)^2}$$

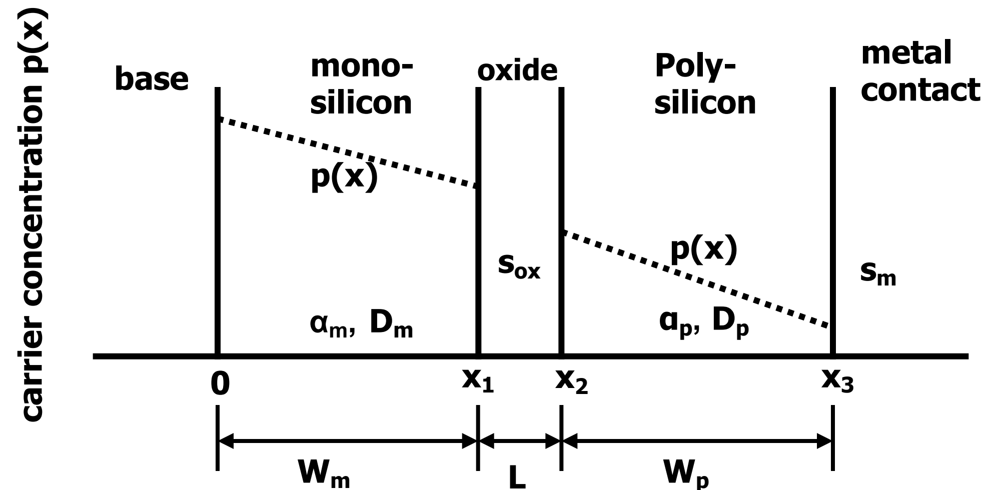
α_m : Hooge parameter in mono-Si

α_p : Hooge parameter in poly-Si

Assumption: $\alpha_m = \alpha_p = \alpha$

$$\frac{p(x_2)}{p(x_3)} \approx 1 + \frac{s_m W_p}{D_p}$$

$$\frac{p(0)}{p(x_1)} = 1 + \frac{W_m}{D_m}\left(\frac{1}{s_{ox}} + \frac{1}{s_m} + \frac{W_p}{D_p}\right)^{-1}$$



Tunneling fluctuation in S_{IB}

$$\frac{S_{I_{BT}}}{I_B^2} = \left[1 + s_{ox}\left(\frac{1}{s_m} + \frac{W_m}{D_m} + \frac{W_p}{D_p}\right)\right]^{-2} \frac{S_{t_{mn}}}{t_{mn}^2}$$

$$\frac{S_{t_{mn}}}{t_{mn}^2} = \frac{m^* qkTL^3 \tan\delta}{3V_o\hbar^2\pi\varepsilon_{ox}Af}$$

t_{mn}	tunneling probability of minority carriers
$S_{t_{mn}}$	fluctuation in t_{mn}
m^*	effective mass of minority carriers
q	electronic charge
k	Boltzmann constant
L	IFO thickness

ε_{ox}	oxide permittivity
V_o	barrier height for the minority carriers
$\hbar$	modified Planck's constant
A	area of IFO
$\tan\delta$	loss tangent of the oxide

Scaling effect on S_{IB}

AF for S_{IB} in PNP transistors

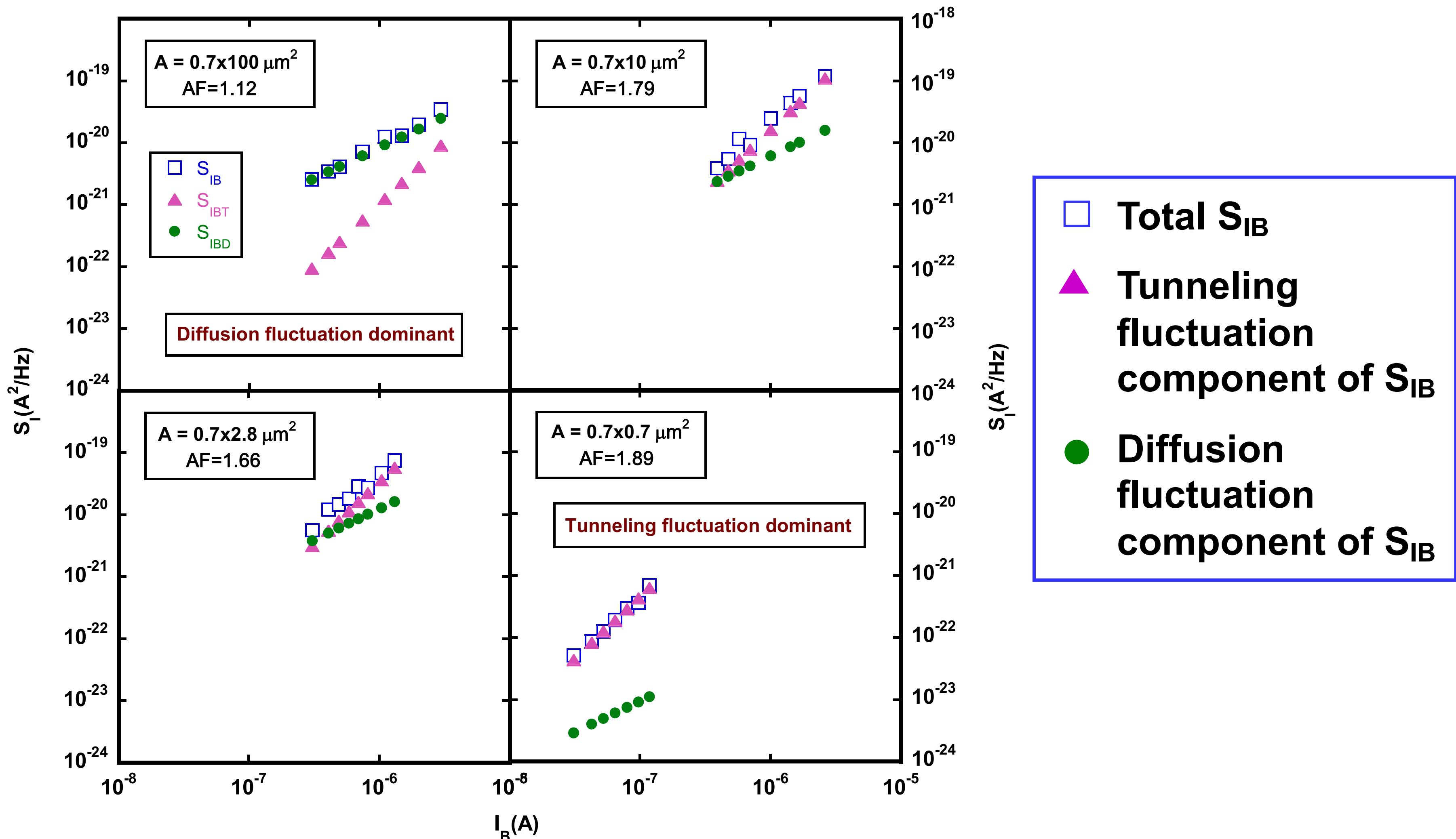
Relative IFO thickness	AF	
	0.7x100 (μm²)	0.7x0.7 (μm²)
thickest	1.12	1.89
medium	1.23	2.09
thinnest	1.01	

$$S_{I_B} = KF \cdot I_B^{AF}$$

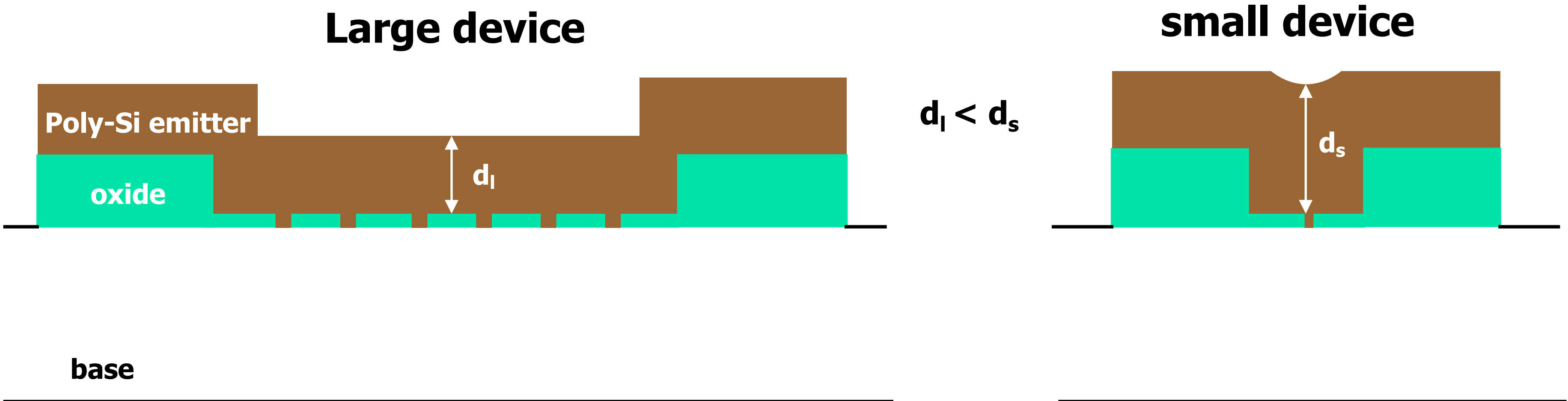
$$S_{I_B} \approx S_{I_{B_{diff}}} + S_{I_{B_{tun}}}$$
$$= KF_D \cdot I_B + KF_T \cdot I_B^2$$

- **Diffusion fluctuation dominant in large (0.7x100μm²) devices.**
- **Tunneling fluctuation dominant in small (0.7x0.7μm²) devices.**

Scaling effect on S_{IB} in PNP transistors with thickest IFO



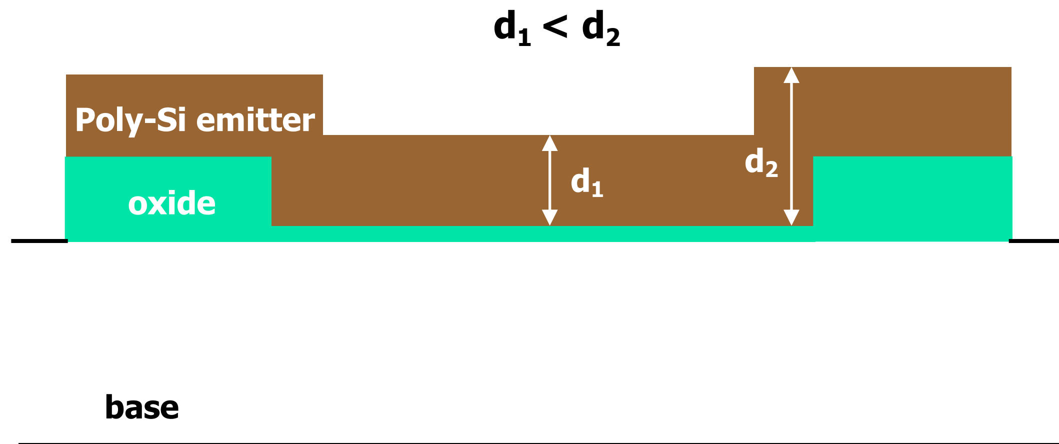
Emitter plug effect in smaller device



- Thicker polysilicon in smaller transistors.
- Lower dopant concentration; shallower junction.
  - higher chance for minority carriers from base to reach and tunnel through the oxide interface; tunneling fluctuation dominant.
  - FLUORINE EFFECT: fluorine enhances oxide break-up.
    - lower fluorine (from BF_2) concentration causes less oxide breakup in smaller PNP devices; increased tunneling:

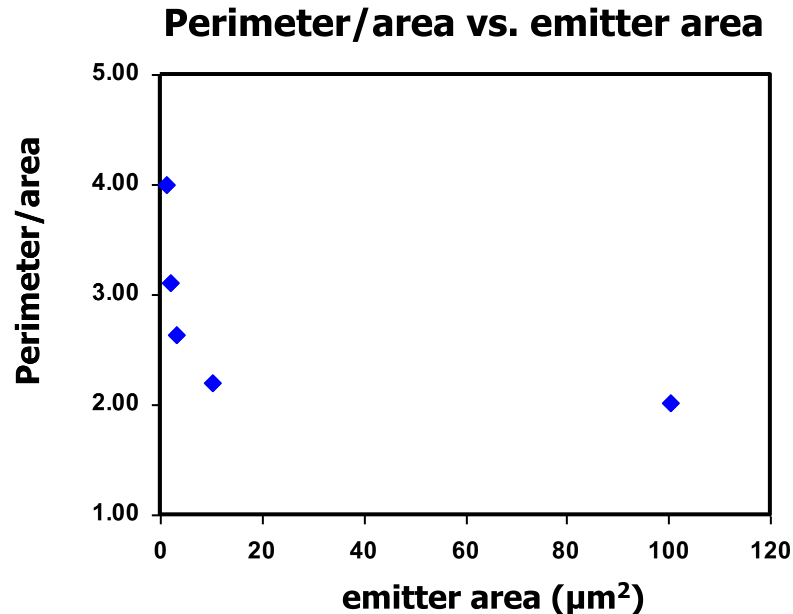
(no fluorine in the transistors studied here)

Perimeter depletion effect



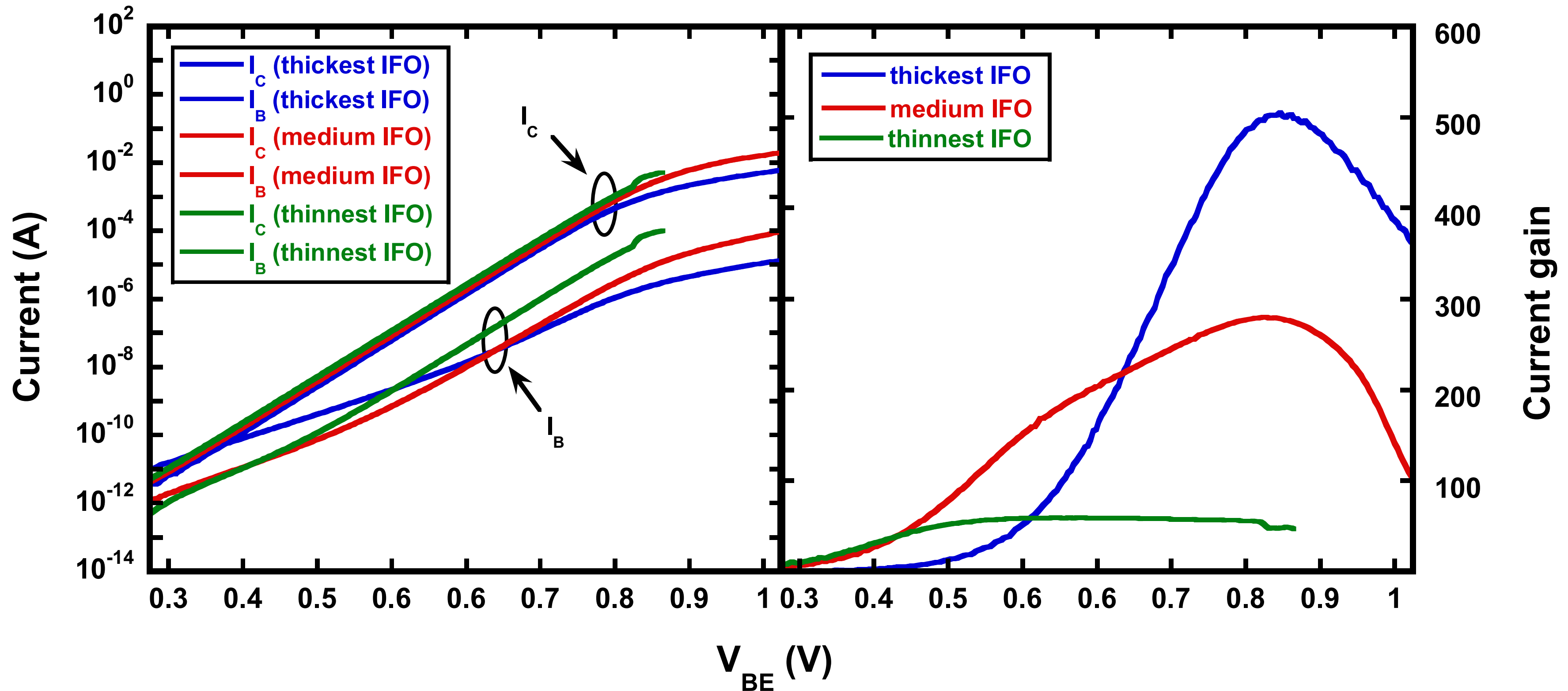
- Polysilicon surface almost perpendicular to wafer surface at emitter window sidewall.
- Reduced doping concentration in the perimeter region.
- Shallower junction close to emitter window perimeter.
- An overlap of the emitter-base space charge region with poly-mono silicon interface might occur close to perimeter.

Perimeter depletion effect in smaller transistors



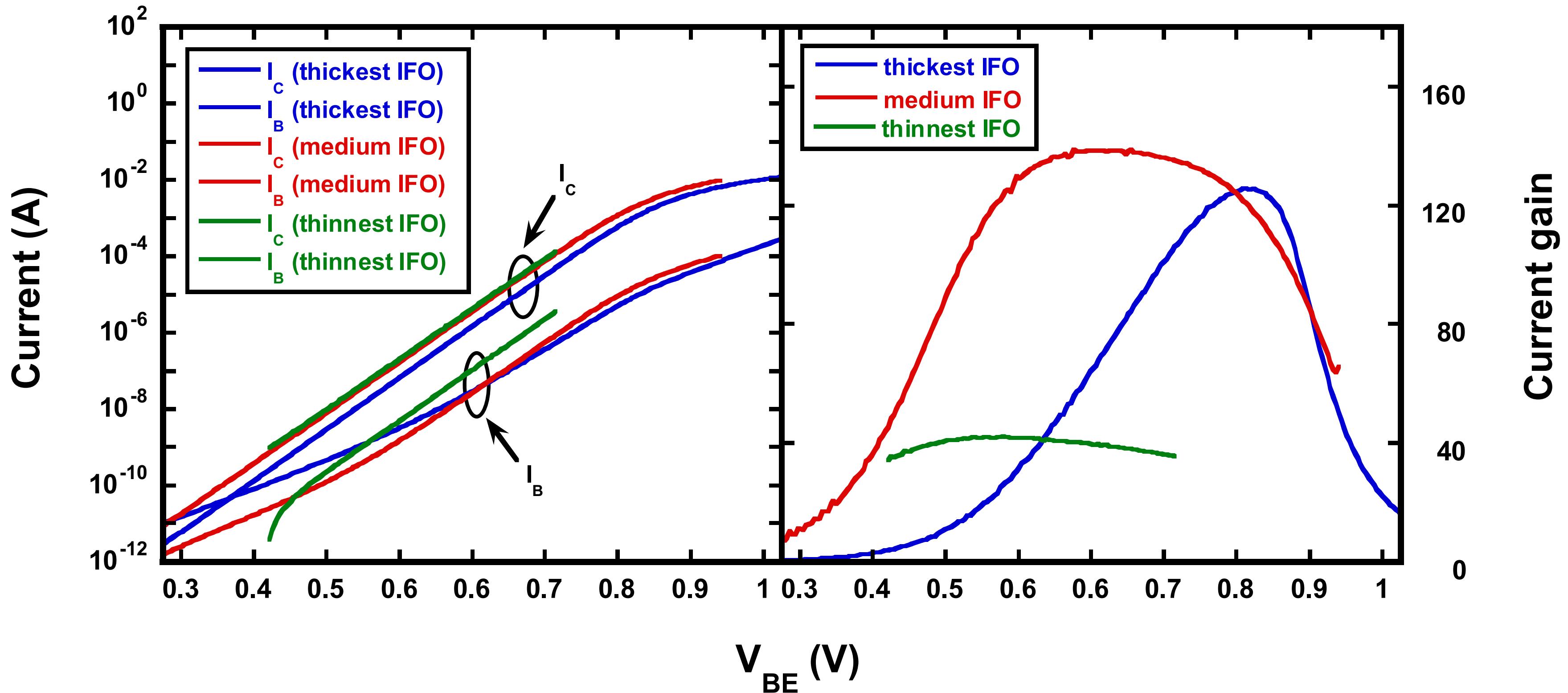
- For smaller transistors
  - perimeter/area ratio increases sharply.
  - non ideal peripheral component of base current increases.
  - fluctuation in non-ideal base current might become significant.

Effect of IFO on DC characteristics of 0.7x100μm² NPN transistors



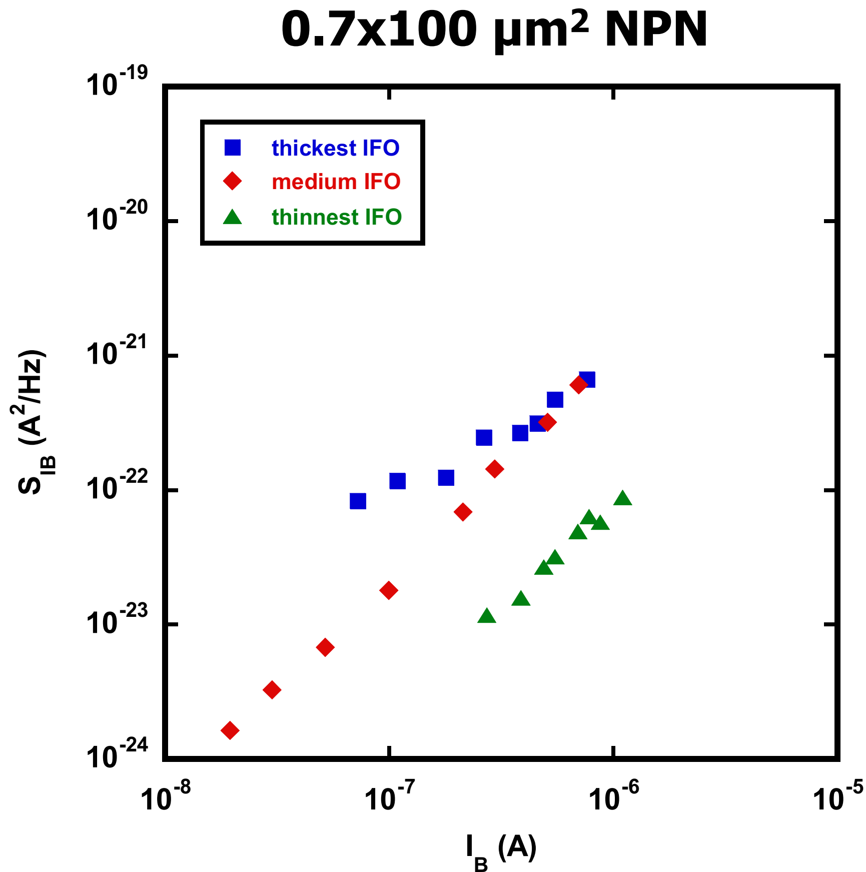
- IFO increases the current gain significantly.

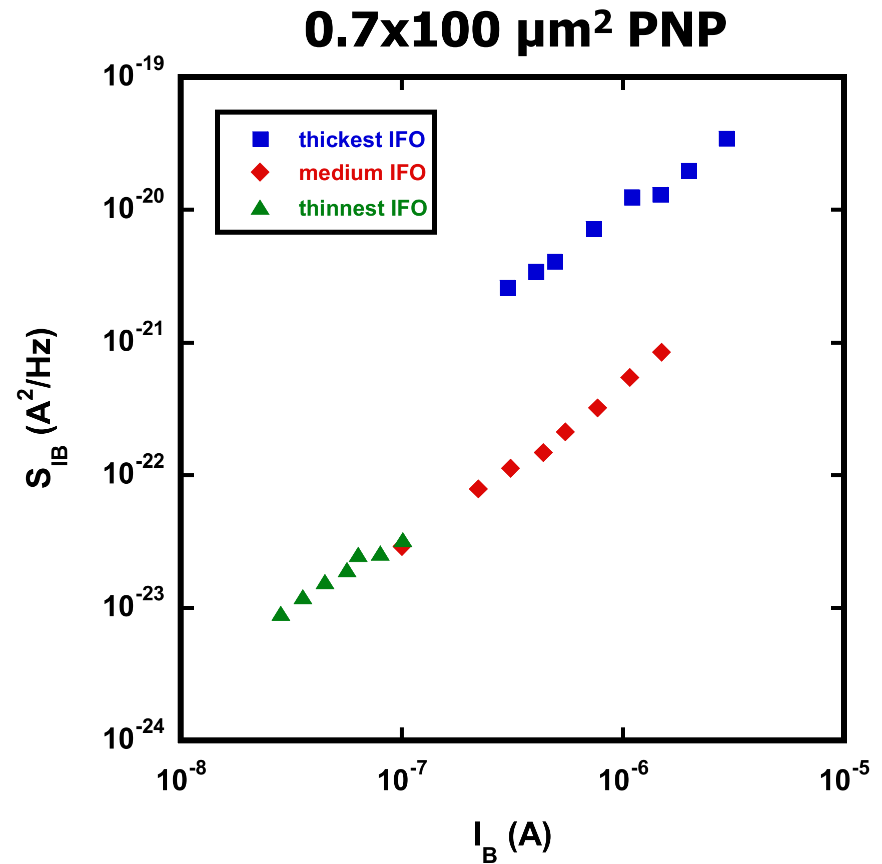
Effect of IFO on DC characteristics of 0.7x100μm² PNP transistors



- **No significant improvement in current gain with increasing IFO thickness.**

Effect of interfacial oxide on S_{IB} in NPN and PNP transistors





- **IFO increases S_{IB} both in NPN and PNP transistors.**

Difference in the effect of IFO in NPN and PNP transistors

0.7x100μm² transistors

Device type	AF
PNP	~ 1
NPN	~ 1.5

$$S_{I_B} = KF \cdot I_B^{AF}$$

$$S_{I_B} \approx S_{IB_{diff}} + S_{IB_{tun}} = KF_D \cdot IB + KF_T \cdot IB^2$$

- **In PNP, diffusion fluctuation in mono and poly-silicon emitter dominates; less effect of IFO.**
- **In NPN, both diffusion fluctuation in mono and poly-silicon emitter, and tunneling fluctuation through IFO contribute.**

Physics behind difference in NPN and PNP transistors

- **Hole barrier height larger than electron barrier height at interfacial oxide:**
  - **minority carriers (holes) severely suppressed in NPN; significant current gain improvement.**
  - **minority carriers (electrons) not suppressed significantly in PNP; little current gain improvement.**
- **Effect of fluorine:**
  - **fluorine accelerates oxide break-up.**
  - **fluorine from emitter dopant BF_2 in PNP creates more oxide breakup; reduced tunneling and increased diffusion through broken oxide.**
- **Increased oxide breakup and faster diffusion of boron makes the emitter deeper in PNP**:
  - **increased recombination-base current, reduced current gain improvement.**
  - **higher diffusion fluctuation in larger monosilicon emitter region.**
- **Different oxidation rate of the base material could create different IFO thickness for NPN and PNP transistors on the same wafer.**

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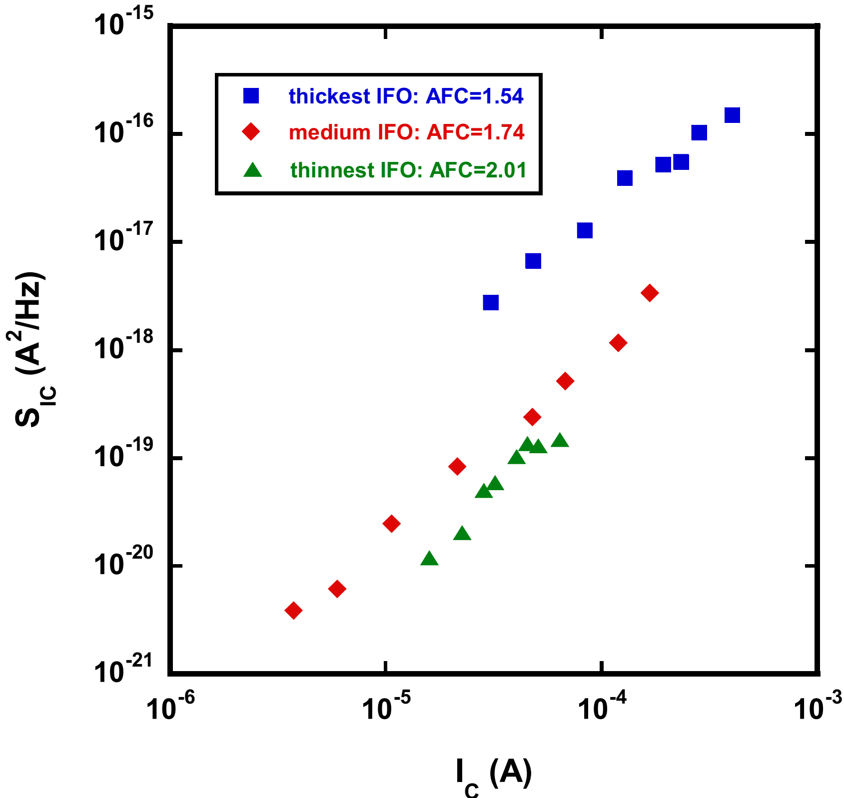
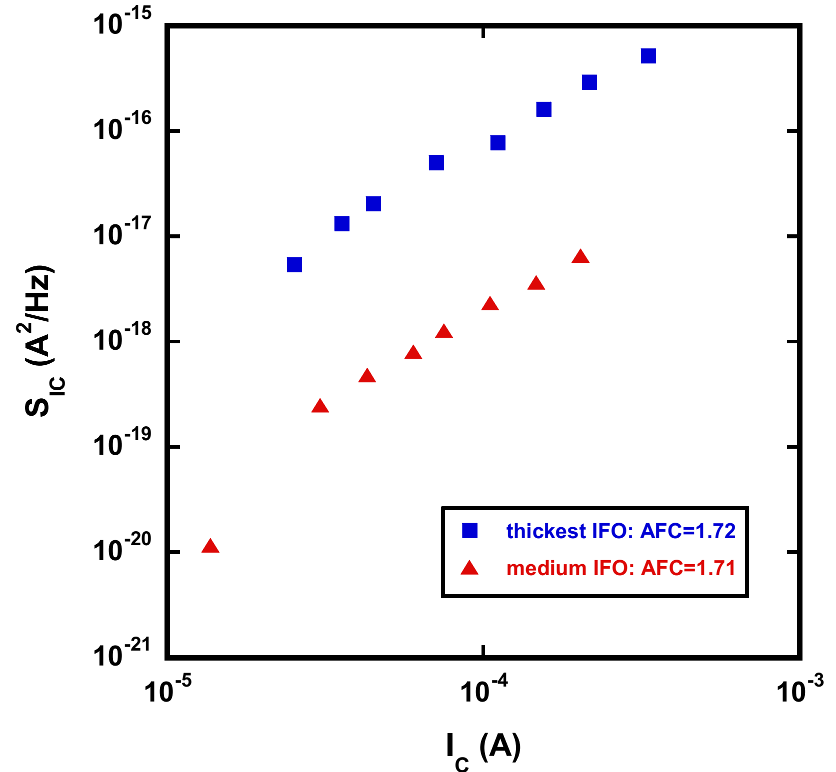
Effect of interfacial oxide on S_{IC}





- **IFO increases S_{IC} both in NPN and PNP transistors.**

S_{IC} modeling

$$S_{I_C} = S_{I_{C_N}} + S_{I_{C_D}} = KF_N \cdot I_C{}^2 + KF_D \cdot I_C$$

Some researchers assign the same origin of S_{IB} to S_{IC}.

$S_{I_C} = \frac{S_{V_C}}{R_L^2}$ is merely an amplified S_{IB}.

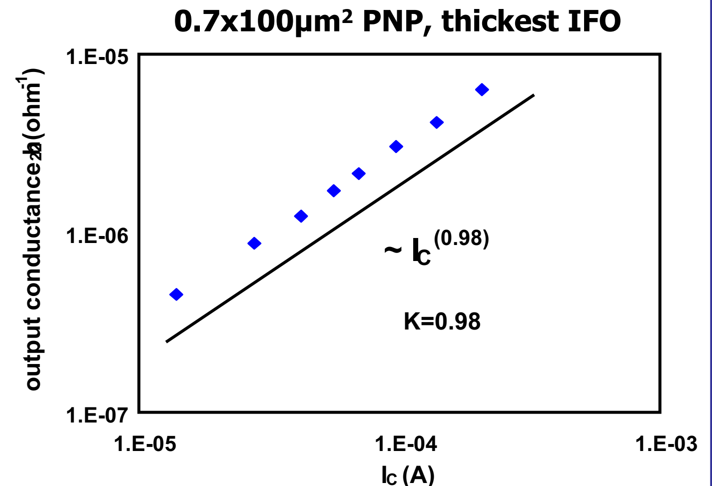
carrier transport determined by electric field in base collector junction.

Hooge type fluctuation at the collector side of base-collector junction.

$$S_{I_C} \propto I_C^{(2K-1)}$$

$$h_{22} \propto I_C^K$$

$$K \geq 1$$



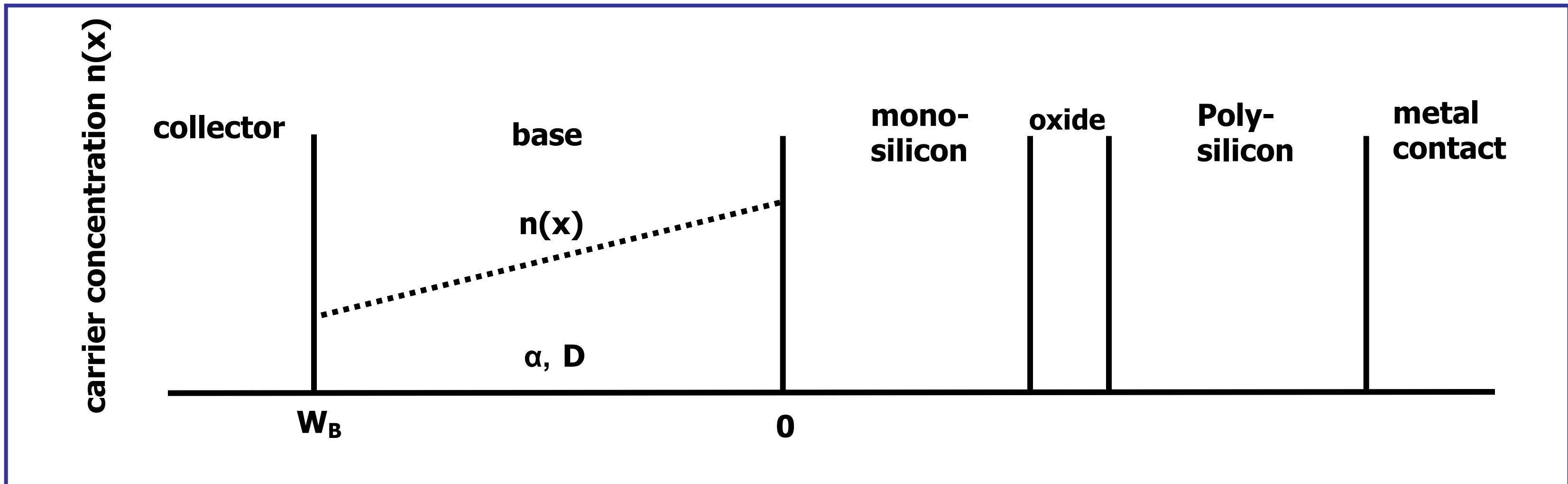
Number fluctuation in S_{IC} requires further investigation.

Diffusion fluctuation in S_{IC}

$$\frac{S_{I_{C_D}}}{I_C} = \frac{qD\alpha}{W_B^2 f} \ln\left(\frac{n(0)}{n(W_B)}\right)$$

$$\frac{n(0)}{n(W_B)} \approx \frac{\upsilon_s + D/W_B}{D/W_B}$$

υ_s **saturated drift velocity**



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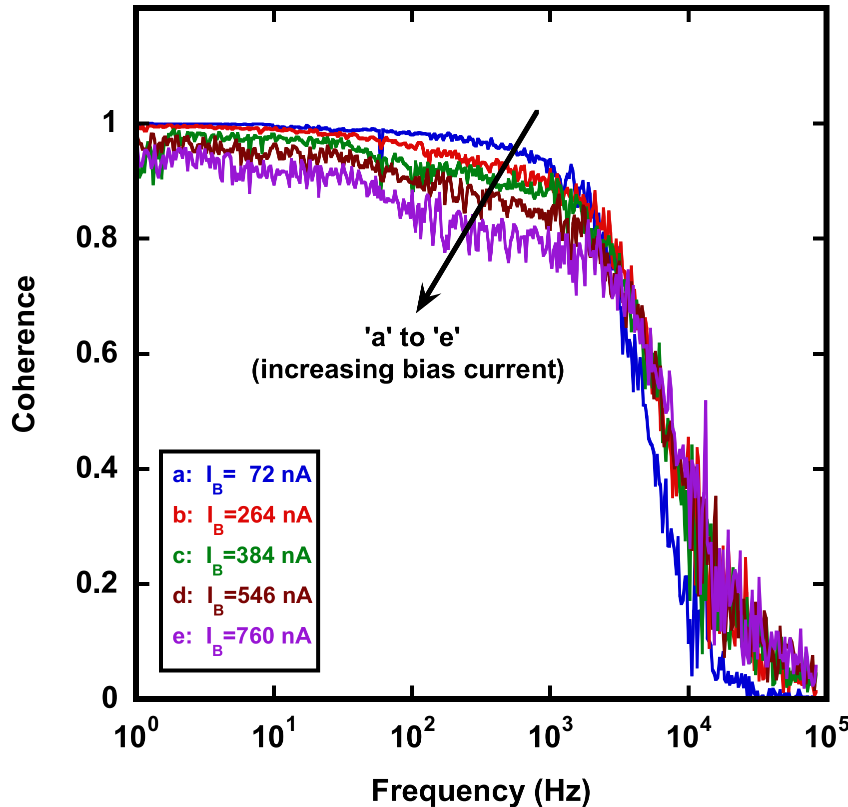
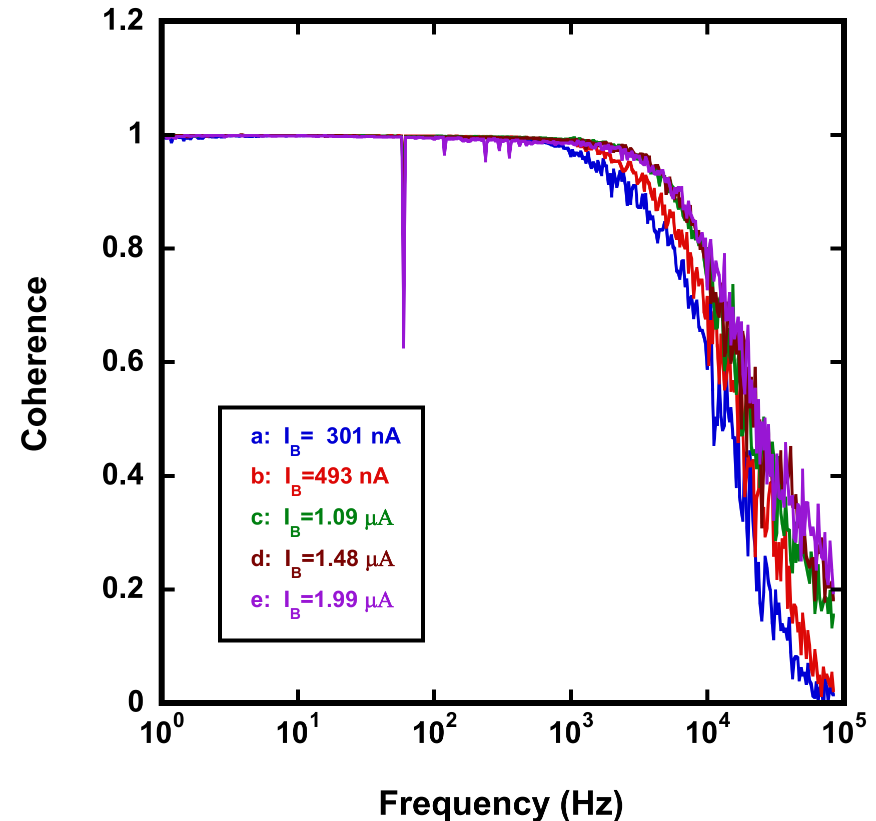
Effect of bias on coherence in NPN and PNP transistors

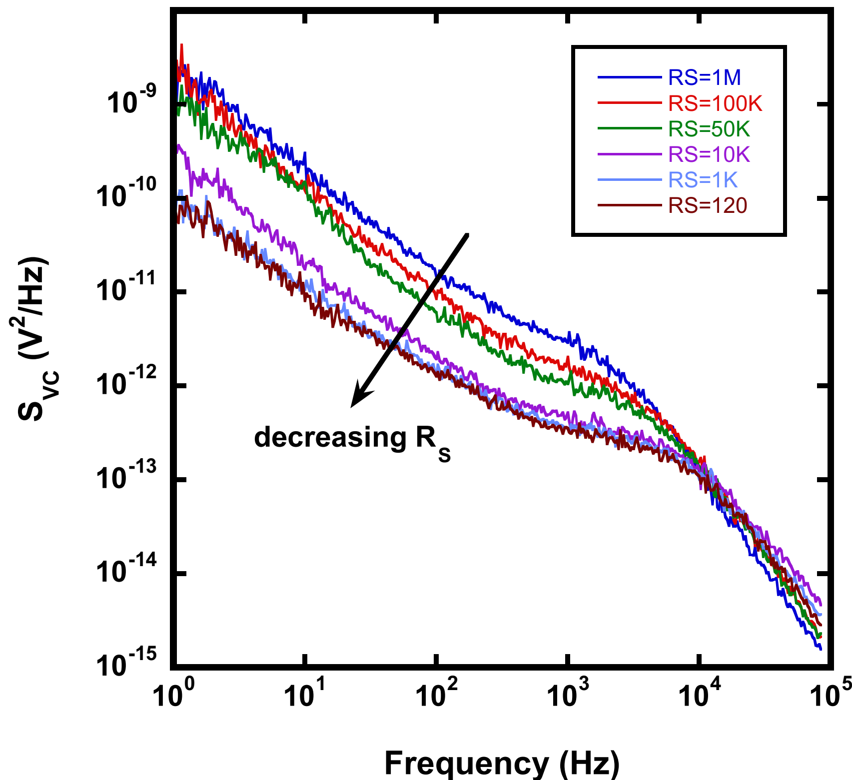


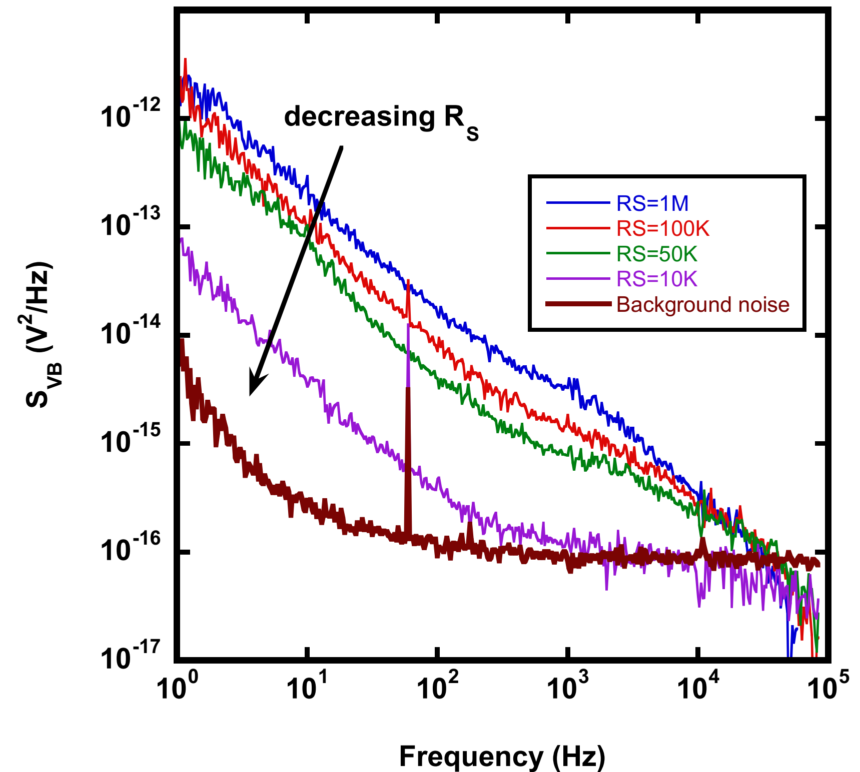


- **Coherence decreases with increasing bias in NPN transistor.**

Effect of varying base bias resistance (R_S) on S_V

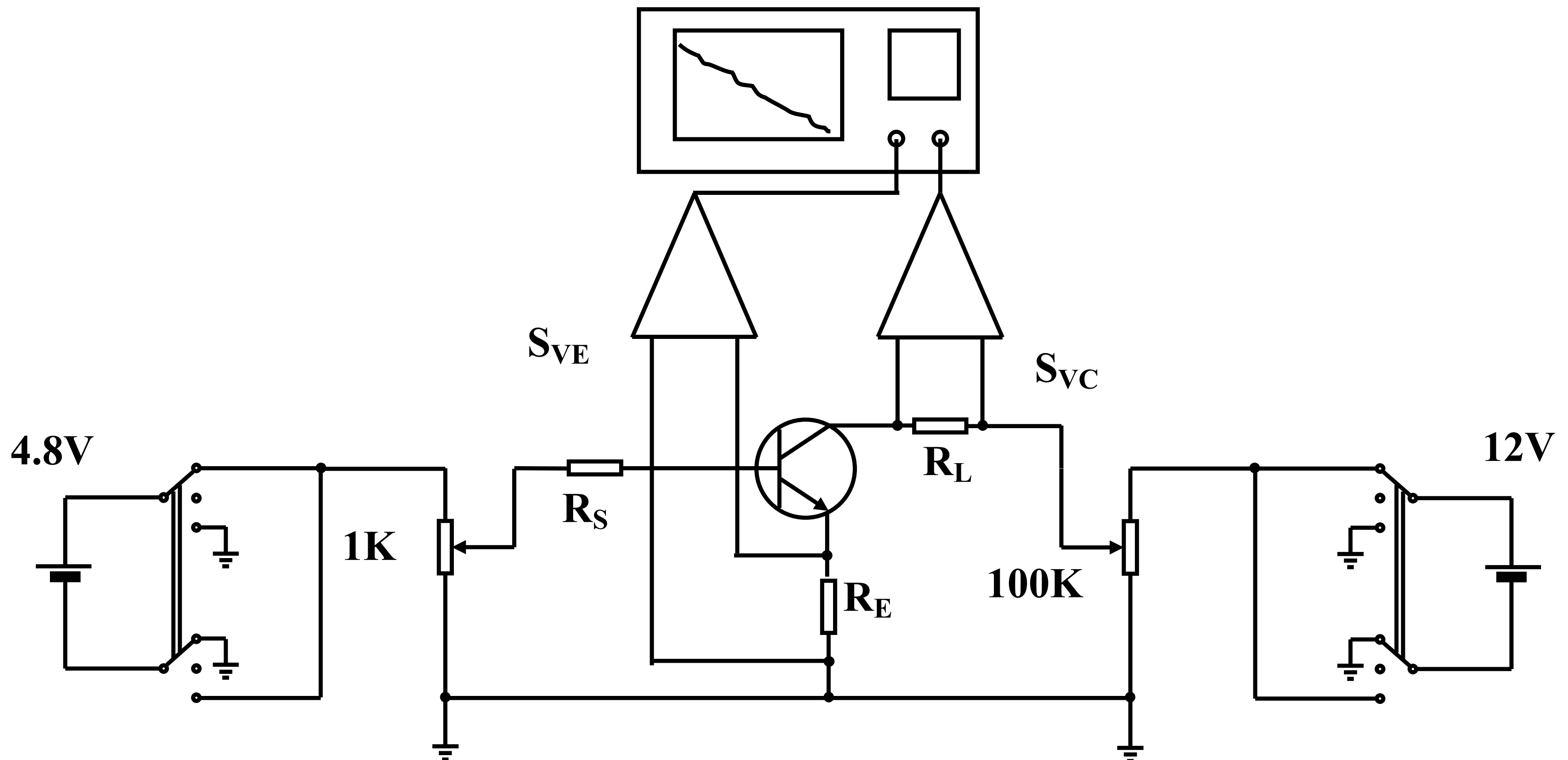
0.7x100 μm² NPN, thickest IFO, IB=384nA



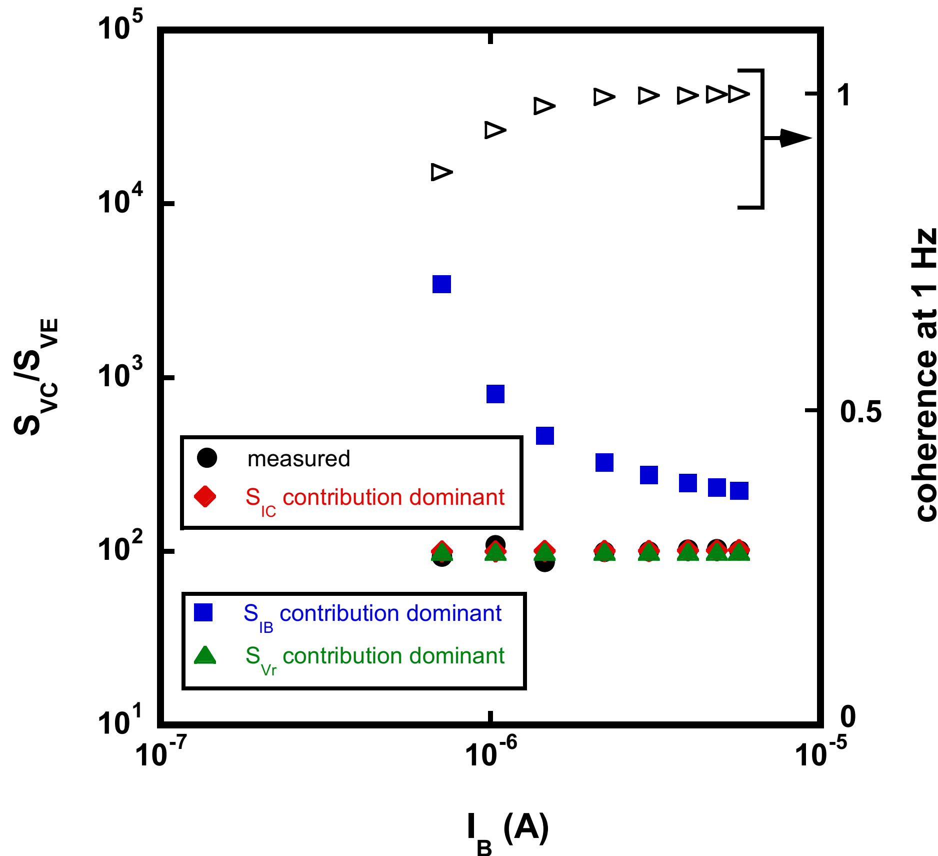


- S_{VC} does not decrease any more for R_S smaller than 1 kΩ.
- S_{VB} becomes comparable to system background noise for R_S smaller than 10 kΩ.

Collector-emitter measurement setup



Dominant noise source in collector-emitter measurement

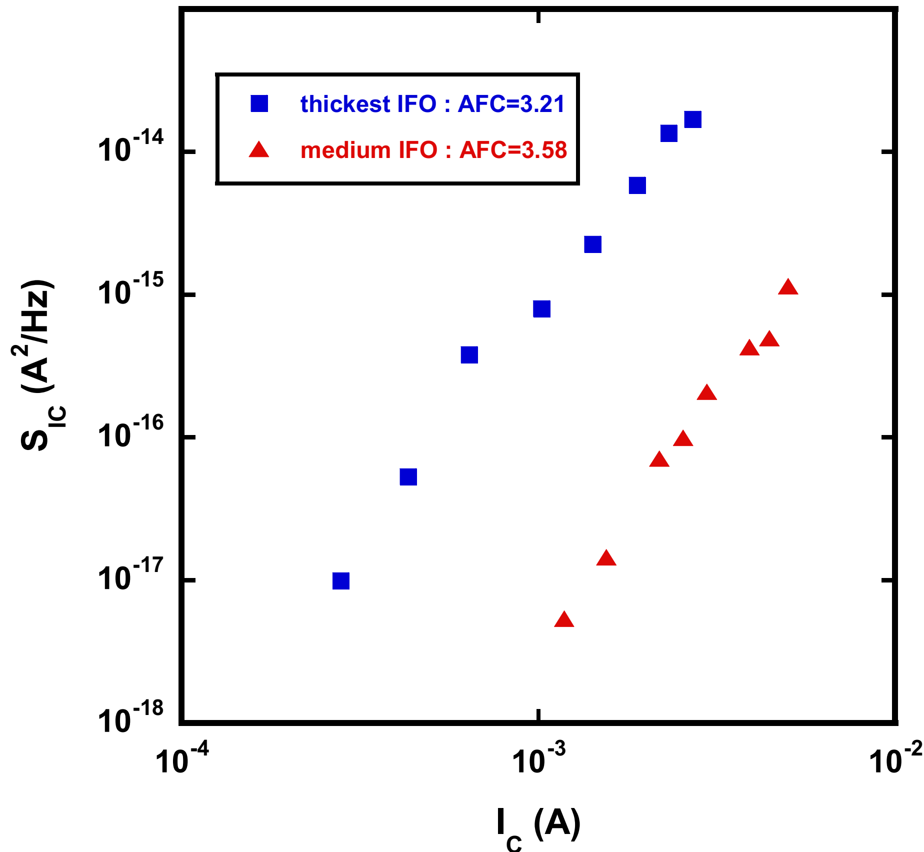


Unity coherence.

One single dominant noise source:

S_{IC} or S_{Vr}?

S_{IC} in collector-emitter measurement



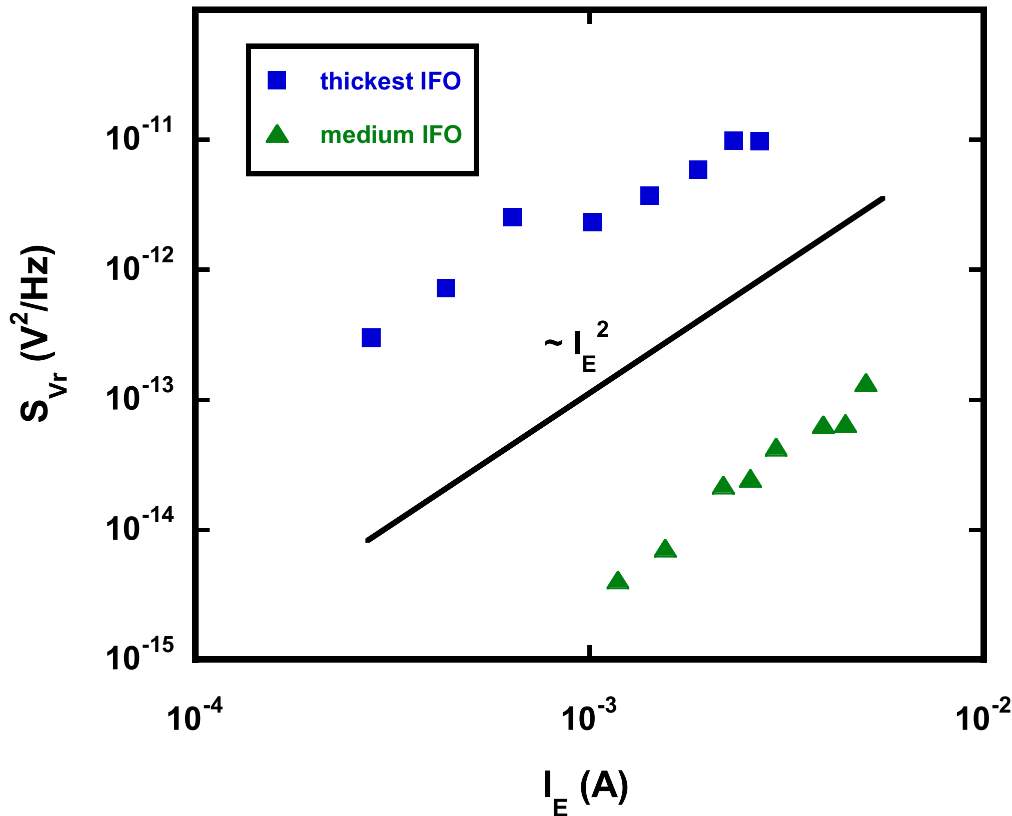
$$S_{I_C} = KFC \cdot I_C^{AFC}$$

$$AFC = 3.05 \sim 3.58$$

no physical explanation for such high current dependence:

SPURIOUS?

Effect of interfacial oxide on S_{Vr}

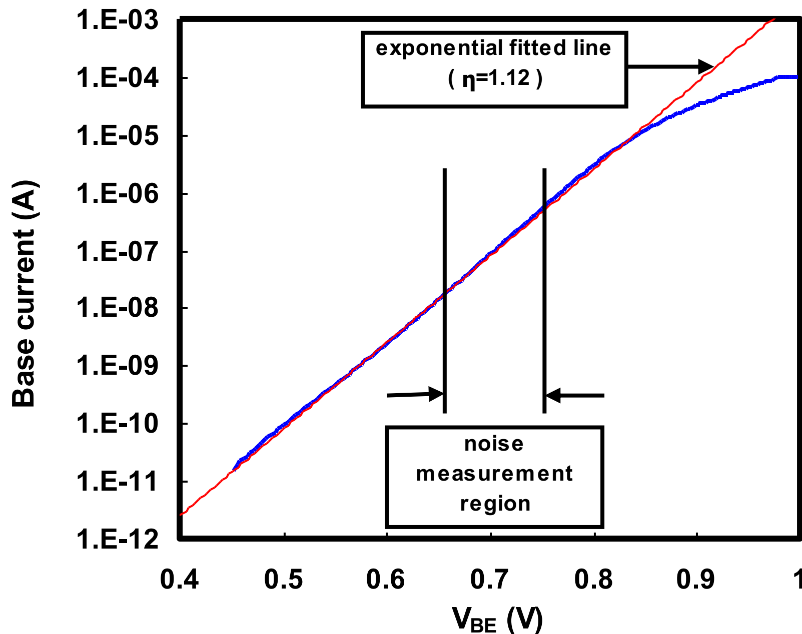


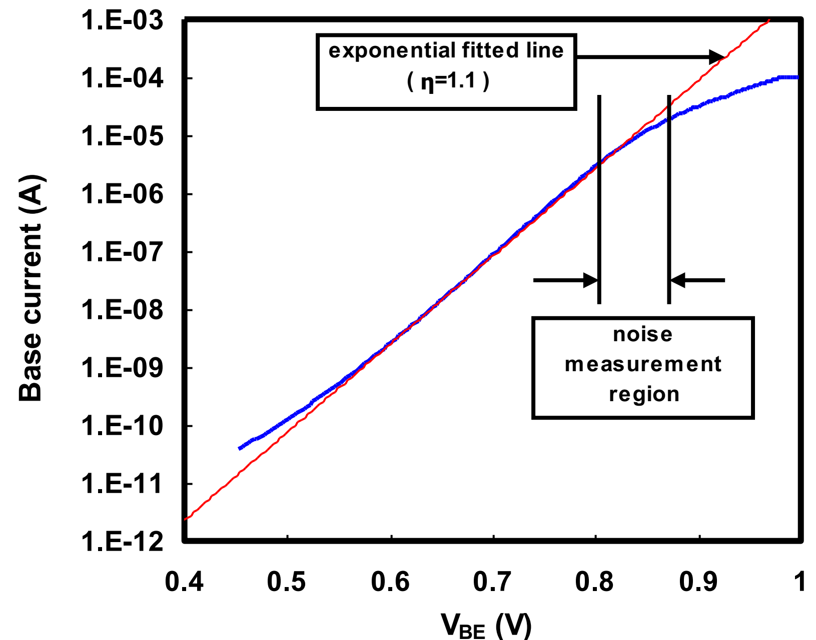
$$S_{V_r} = S_{V_{r_e}} + S_{V_{r_b}}$$

$$S_{V_r} \approx S_{V_{r_e}}$$
$$= I_E^2 \cdot S_{r_e}$$

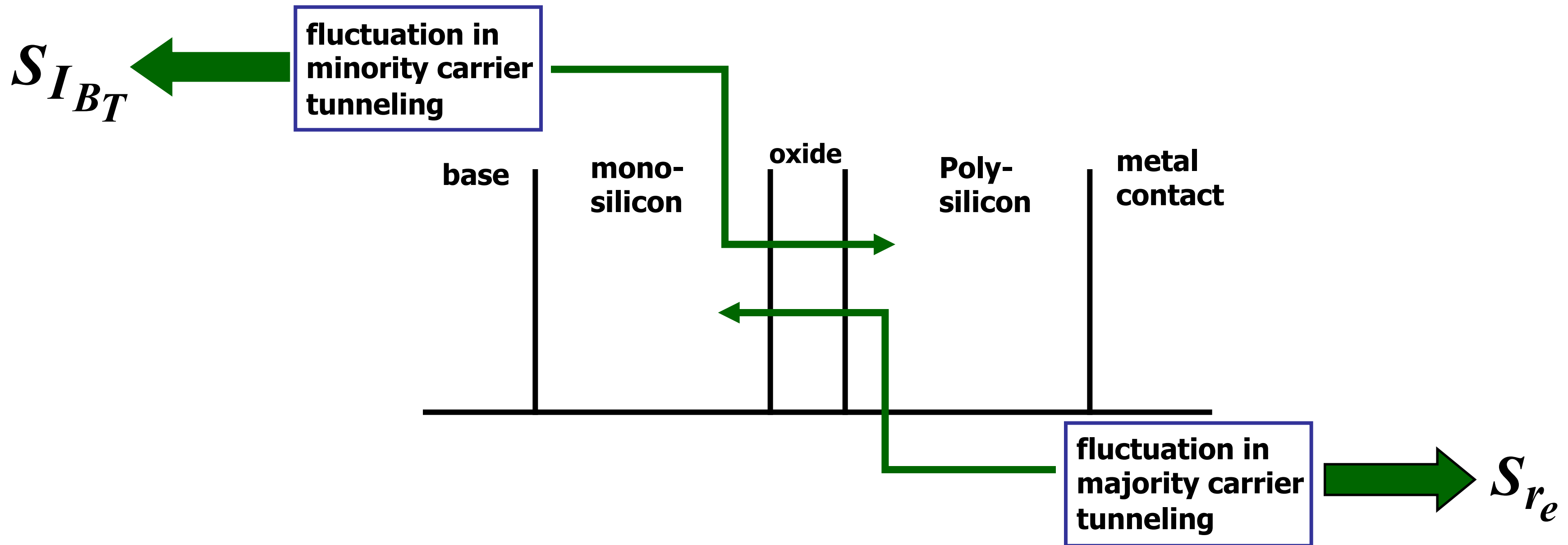
Effect of internal resistance in collector-emitter measurement

0.7x100 μm² NPN, thickest IFO





Tunneling fluctuation through interfacial oxide



$$\frac{S_{r_e}}{r_e^2} = \frac{S_{t_{mj}}}{t_{mj}^2} = \frac{m^* qkTL^3 \tan\delta}{3V_o \hbar^2 \pi \varepsilon_{ox} Af}$$

t_{mj} tunneling probability of the majority carriers through IFO

$S_{t_{mj}}$ fluctuation in t_{mj}

Interfacial oxide thickness

Relative IFO thickness	Emitter area (μm^2)	interfacial oxide thickness (Å) from		
		minority carrier fluctuation (S_{IBT})		majority carrier fluctuation (S_{Vre})
		PNP	NPN	NPN
thickest	0.7x100	14.50		4.08
	0.7x10	16.90		
	0.7x2.8	14.50		
	0.7x0.7	11.00		
medium	0.7x100	4.13	11.30	2.26
	0.7x0.7	8.78		
thinnest	0.7x100		2.70	
	0.7x0.7		2.81	

Inconsistency:

uncertainty in loss tangent, mass and potential barrier of the carriers at oxide interface.

$V_h = 0.363V$ $\quad$ $V_e = 0.097V$

$m_h^* = 0.81m_o$ $\quad$ $m_e^* = 1.08m_o$

$\tan\delta$ **obtained from Kleinpenning et. al, IEEE Trans. on Elec. Dev., vol. 42, 1995.**

V_h **as high as 1.8V and** V_e **as high 1 V found in literature.**
$\tan\delta$ **unique for each sample.**

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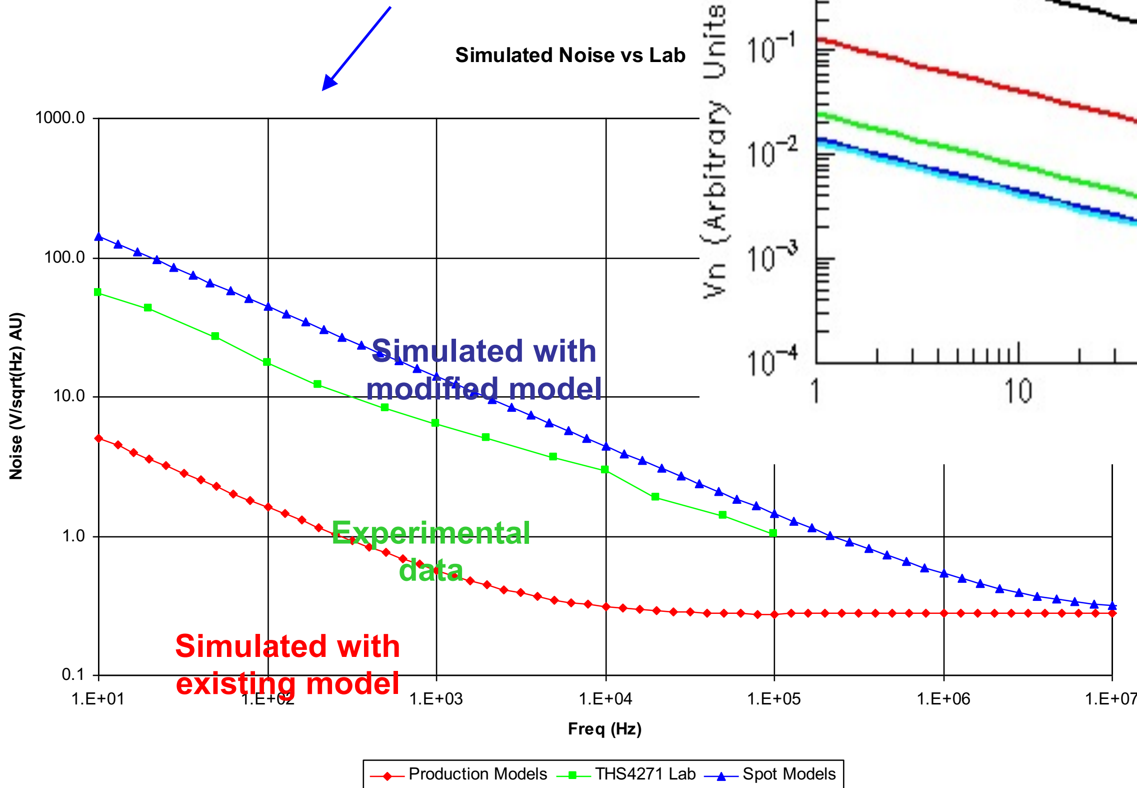
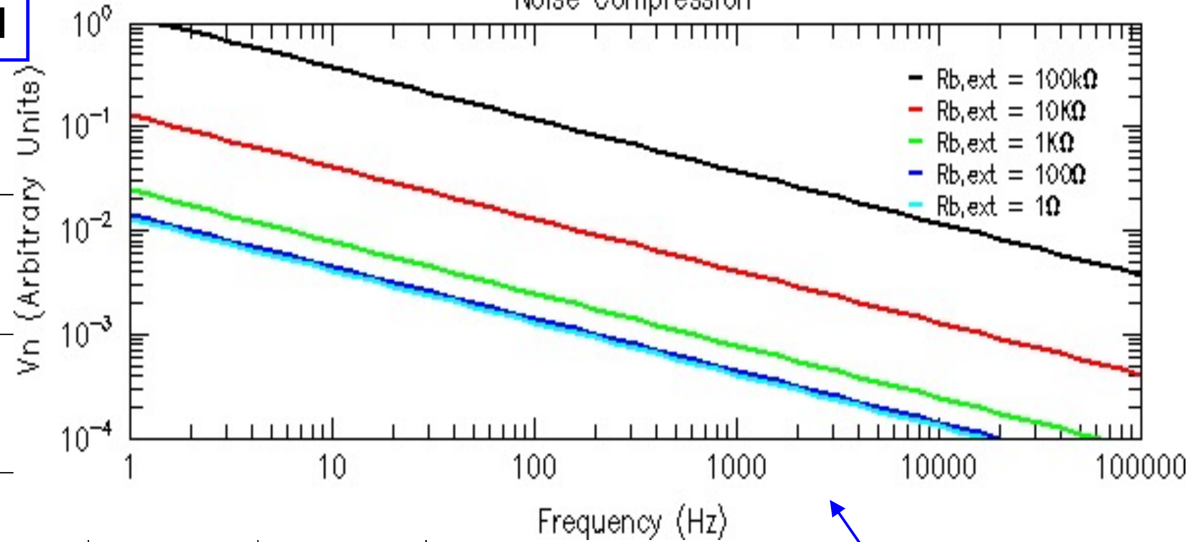
Experimental and Simulated data

Simulation results vs. Measured





Noise data measured at TI

Computer source code

- **Existing BERKELEY SPICE source code has been modified.**
  - **Source code written at Texas Instruments Inc. by Douglas Weiser.**
  - S_{I_C} **and** S_{V_r} **have been added to the existing noise model in addition to** S_{I_B} **.**
  - **An area scaling factor has been added to the equations to make the noise models scalable.**

The modified BERKELEY SPICE source code is available to the SRC (Semiconductor Research Corporation) member companies (TI, Intel, IBM, Motorola, National Semiconductor Corporation, AMD, etc.)

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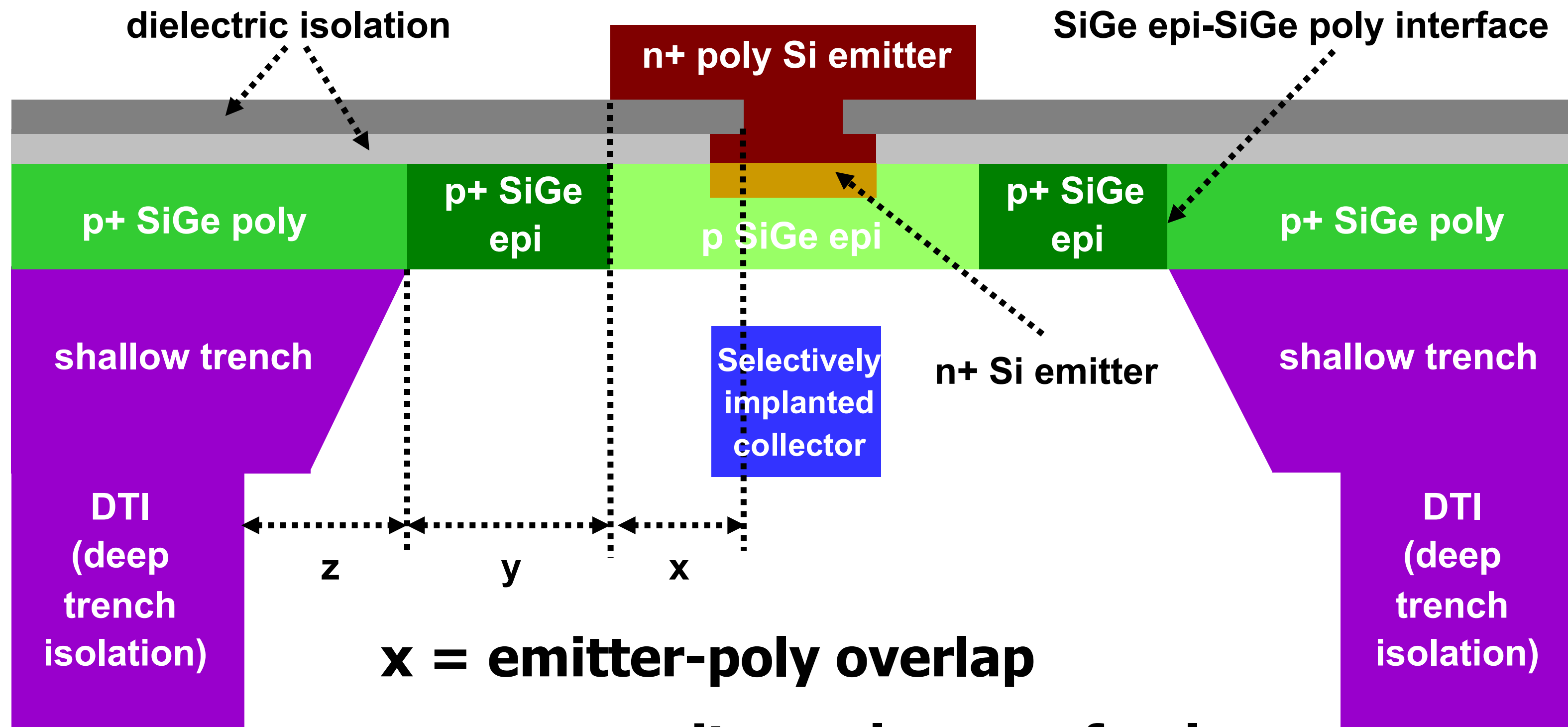
Device structure under investigation



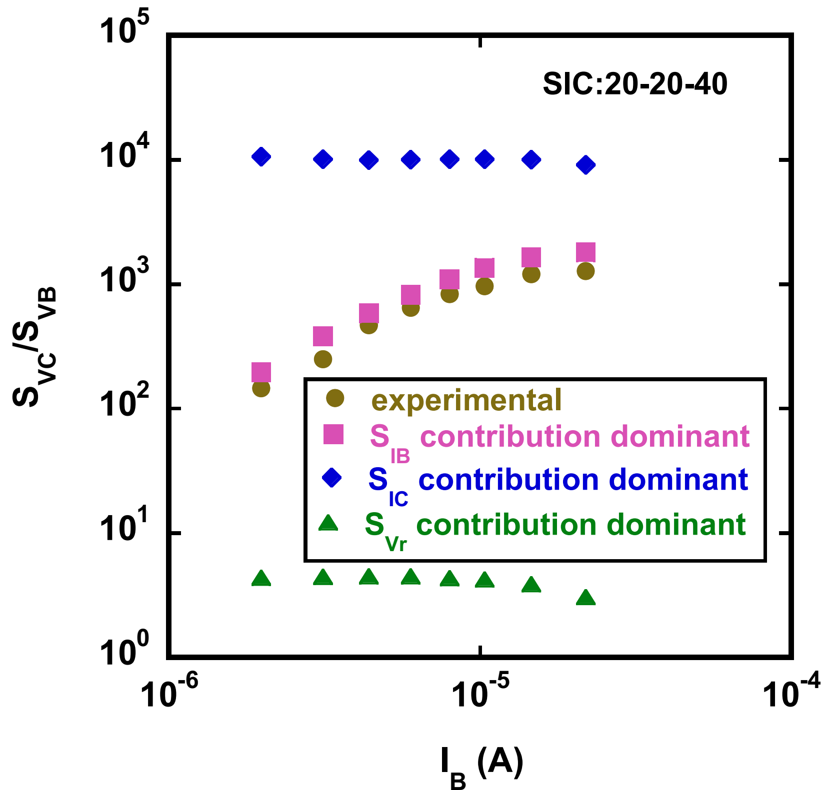
x = emitter-poly overlap

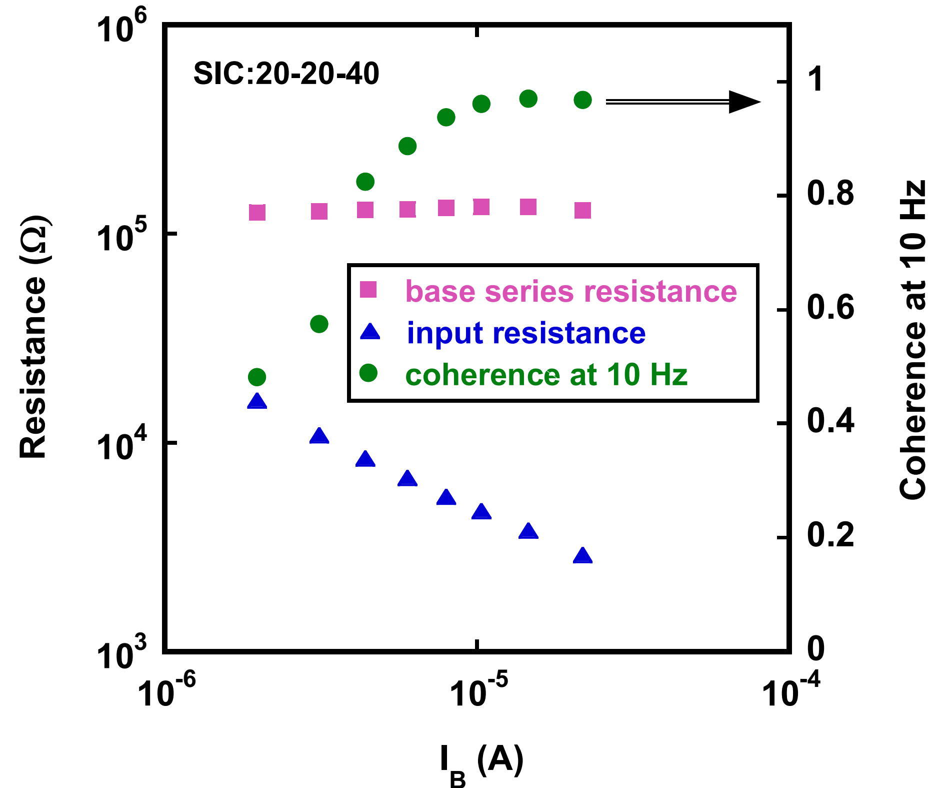
y = composite enclosure of poly

z = DTI enclosure of composite

Transistors described as x-y-z; e.g. SIC:25-10-25.

Dominant noise source





- Calculated S_{VC}/S_{VB} with S_{IB} contribution dominant closely matches experimental S_{VC}/S_{VB} ; S_{IB} contribution dominant.
- I_B increases → r_π decreases → coherence increases.

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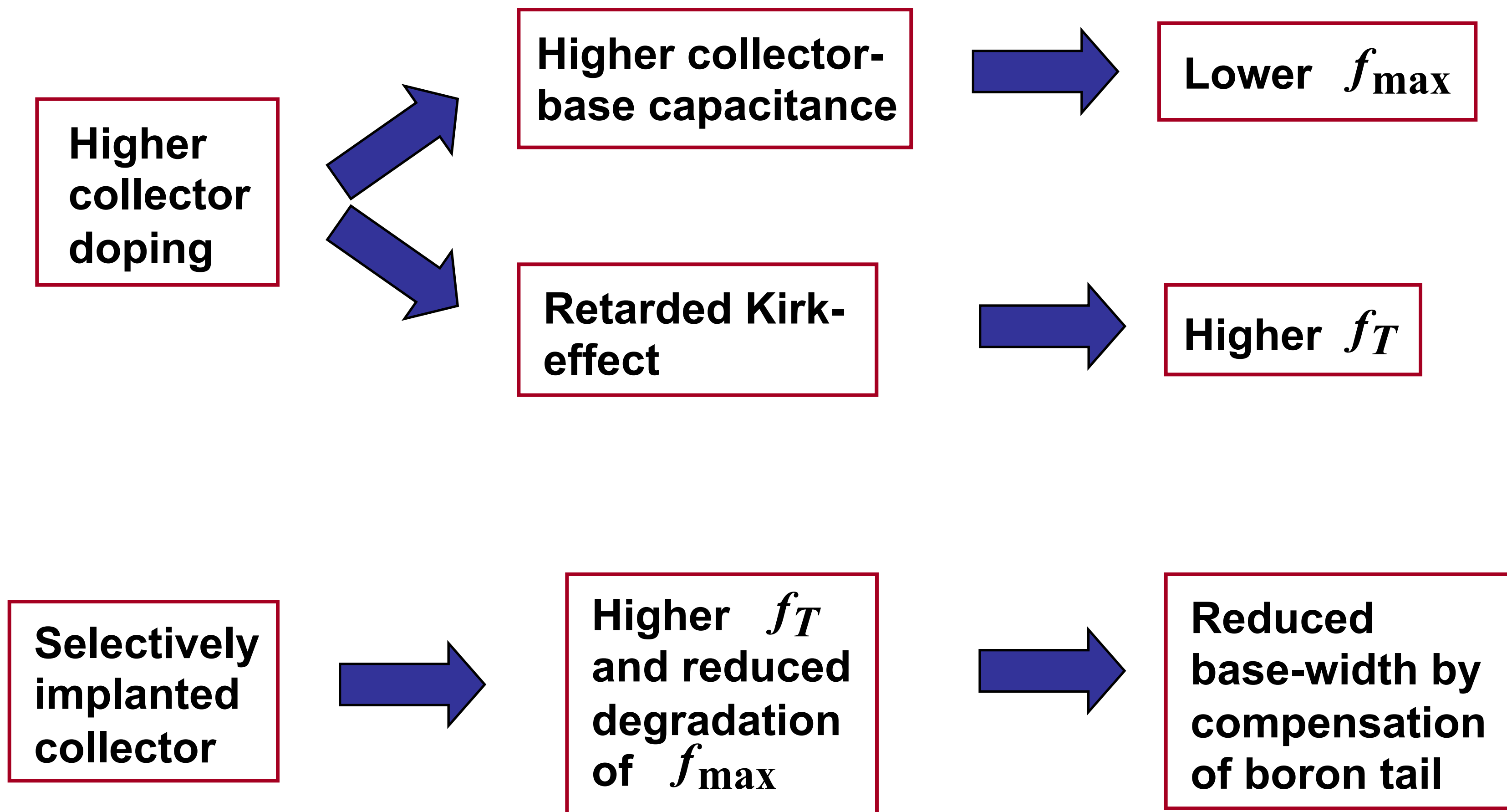
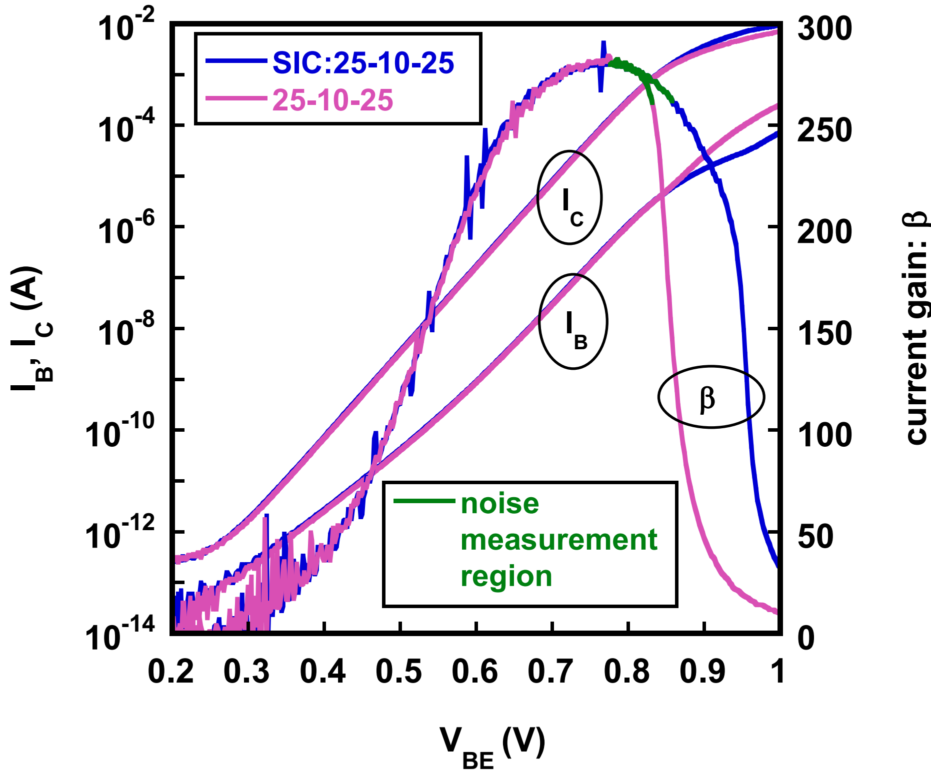
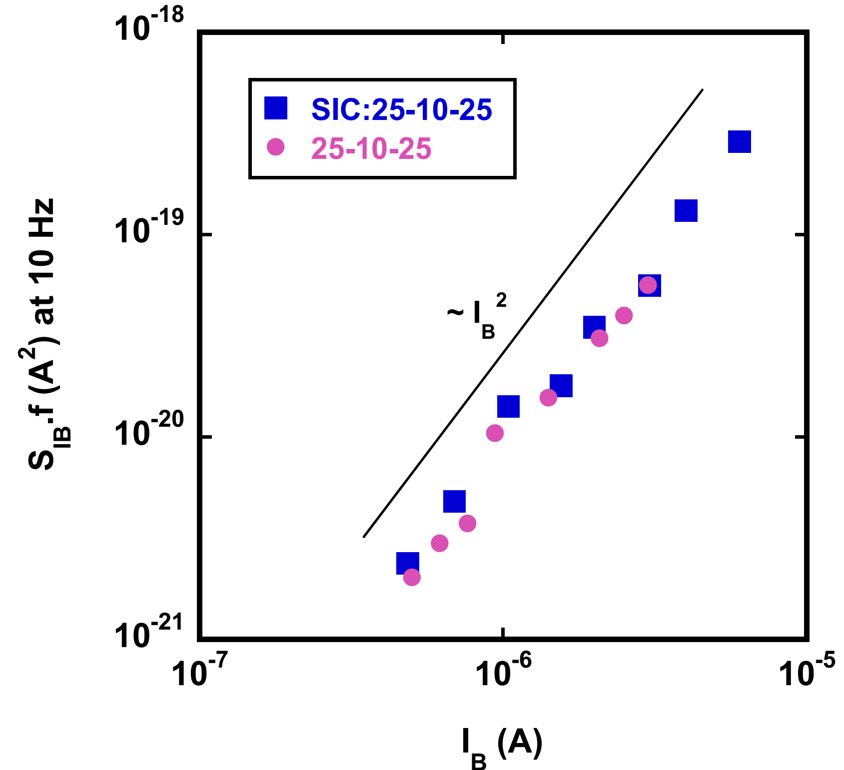
Selectively implanted collector (SIC)



Effect of selectively implanted collector





- **SIC retards Kirk-effect → higher β for wider range of bias.**
- **No degradation in noise.**

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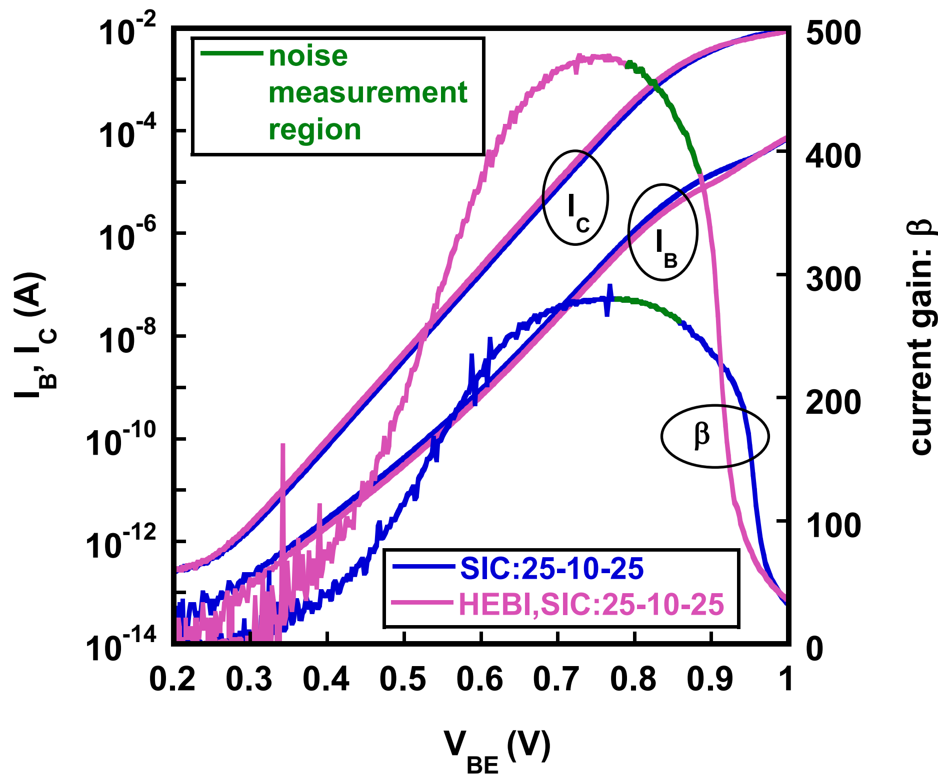
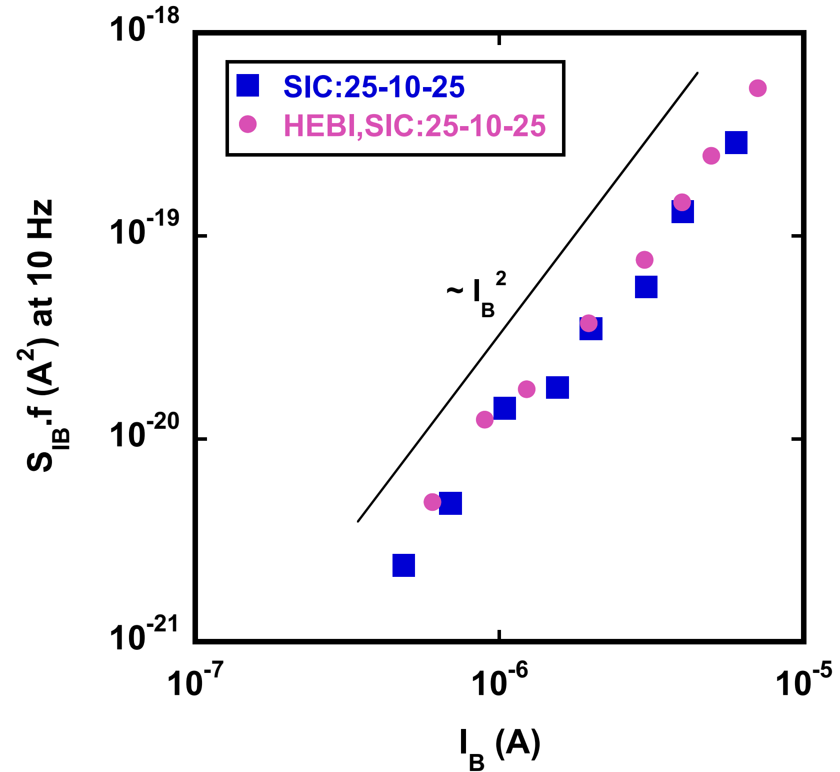
Higher extrinsic base implant (HEBI)

Effect of higher extrinsic base implant





- **Higher gain for higher extrinsic base implant is possibly due to relative changes in Ge profile.**
- **No degradation in noise.**

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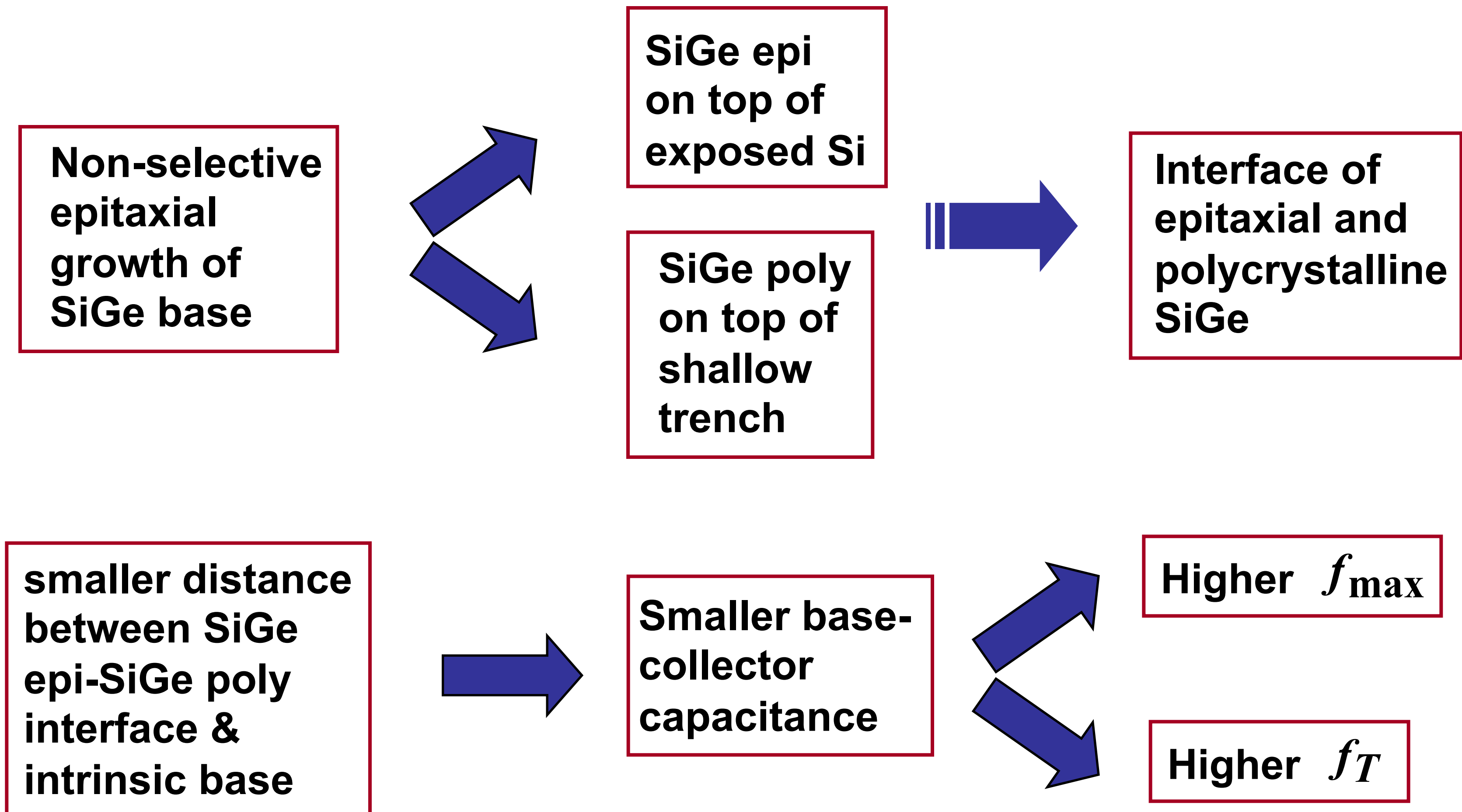
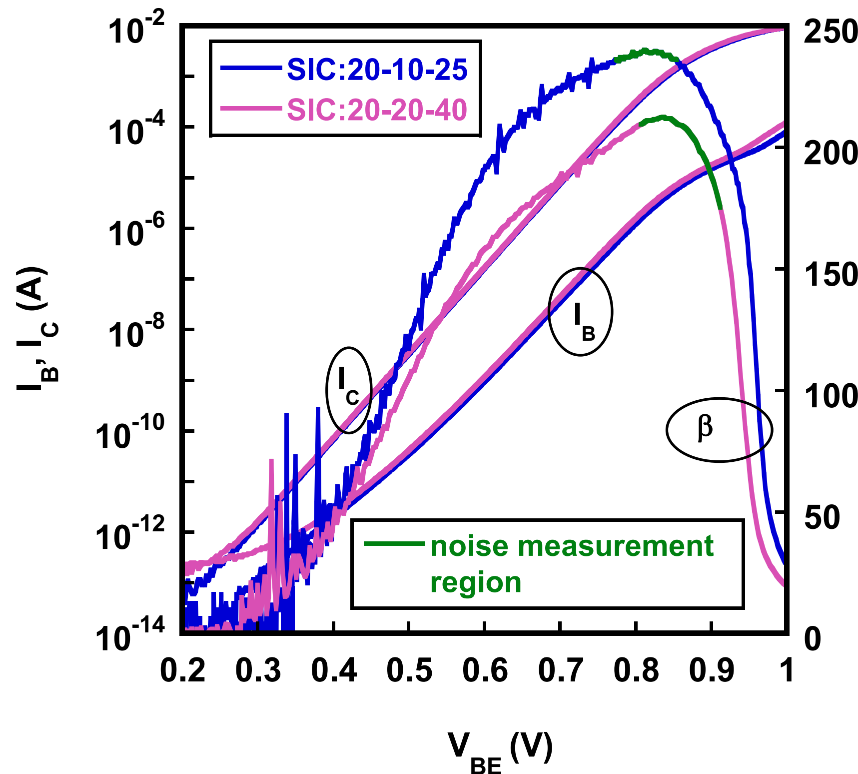
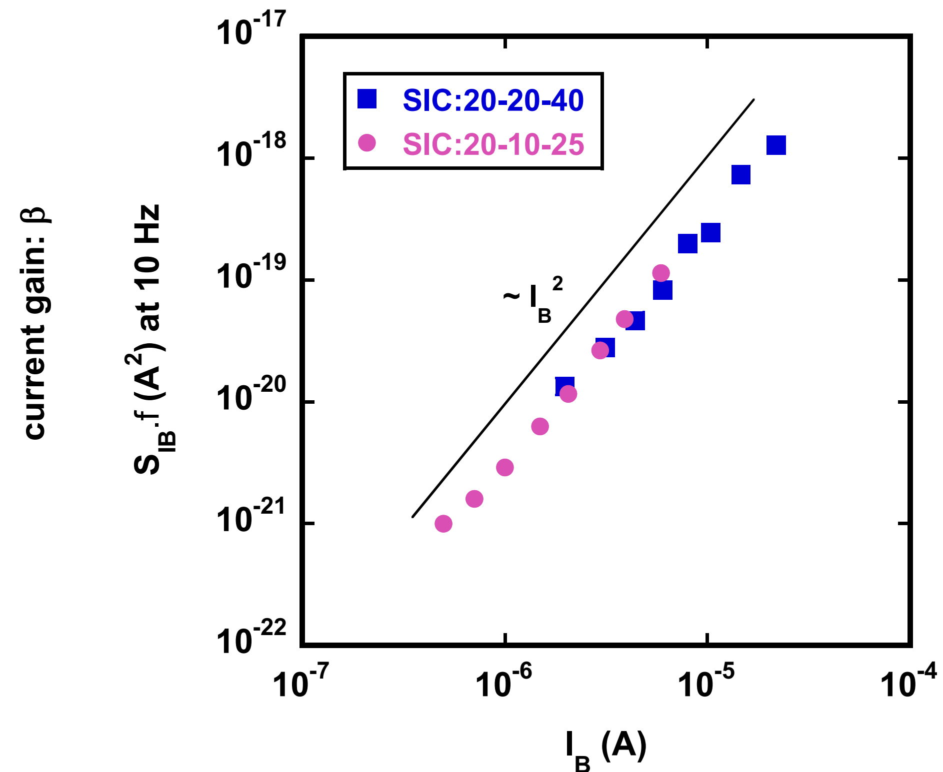
SiGe epi-SiGe poly interface



Effect of SiGe epi-SiGe poly interface





- No significant impact on DC characteristics.
- No degradation in noise; boron implantation in extrinsic base passivates the interface-defects.

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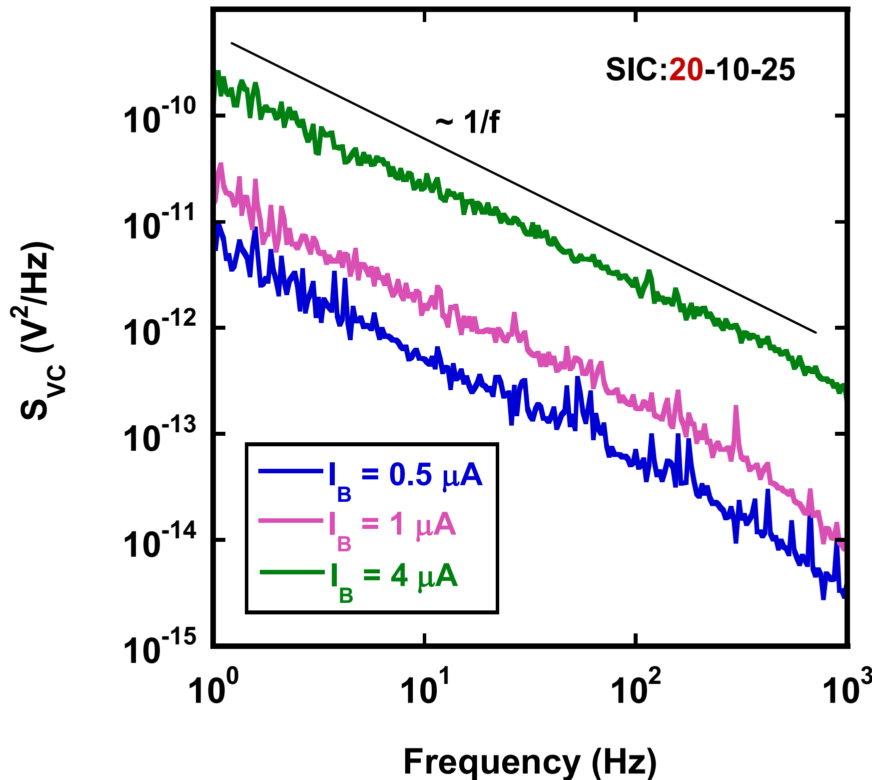
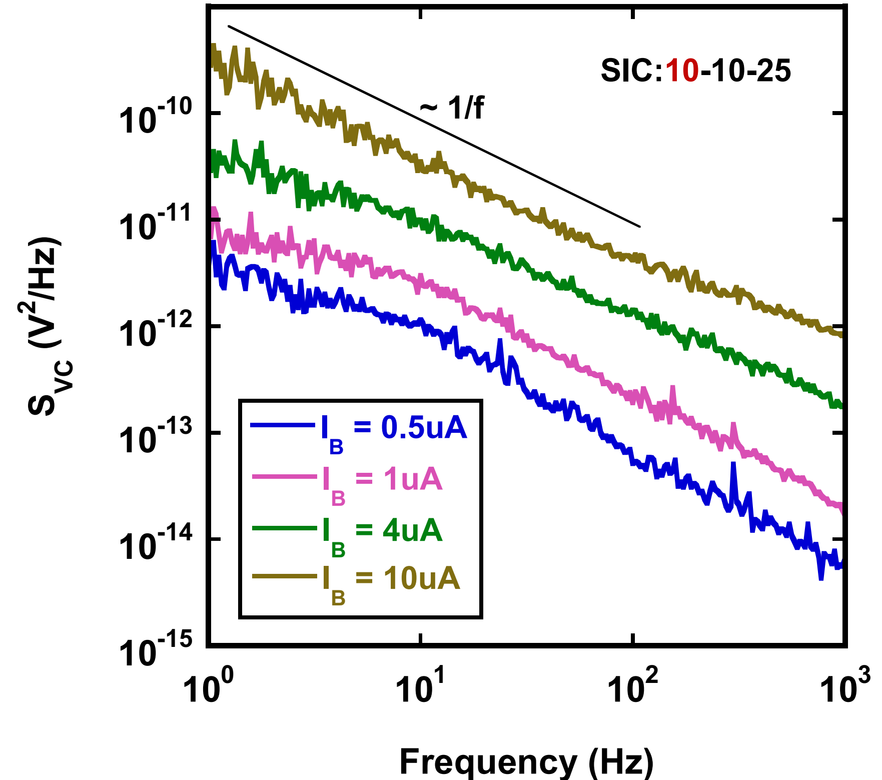
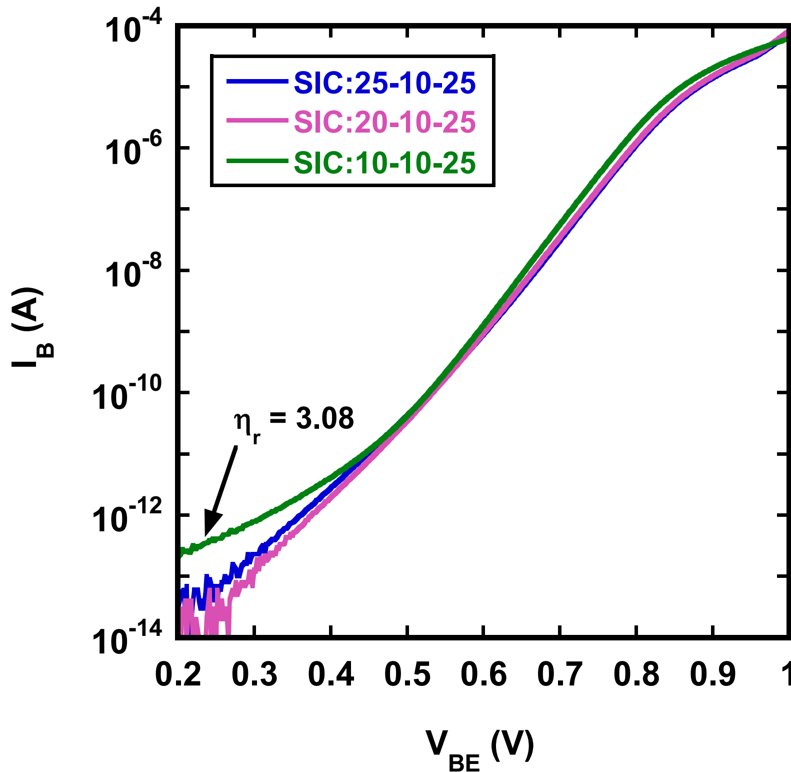
Effect of emitter-poly overlap

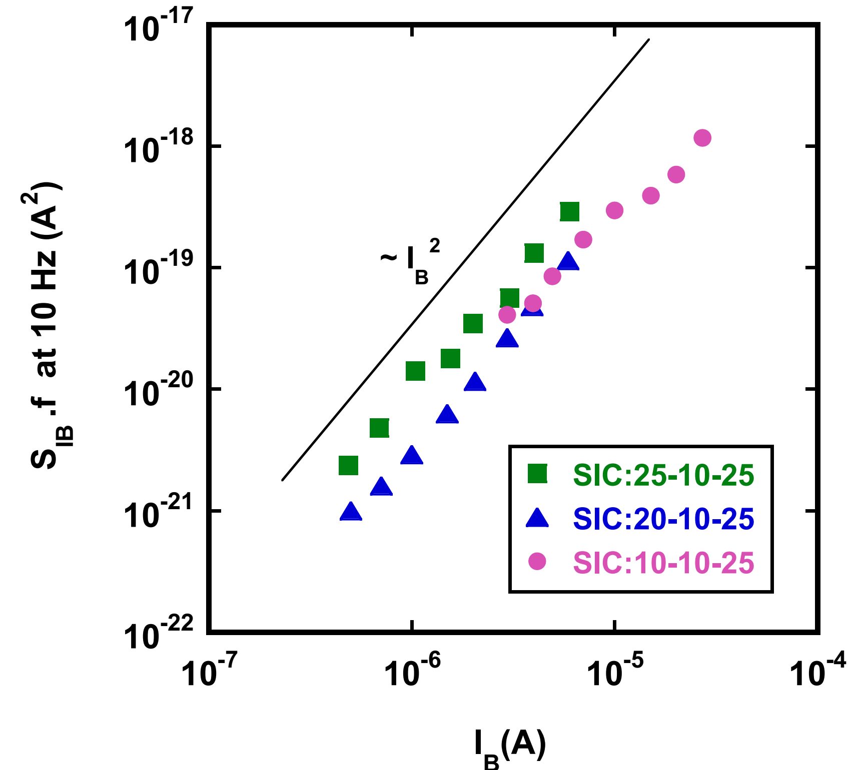




- **Significant g-r noise for smaller emitter-poly overlap.**
- **g-r noise diminished at higher currents in comparison to increased 1/f noise.**

Effect of emitter-poly overlap (cont.)





- **Higher non-ideal base current for smaller emitter-poly overlap.**
- **S_{IB} deviates from $\sim I_B^2$ dependence for smaller emitter-poly overlap.**

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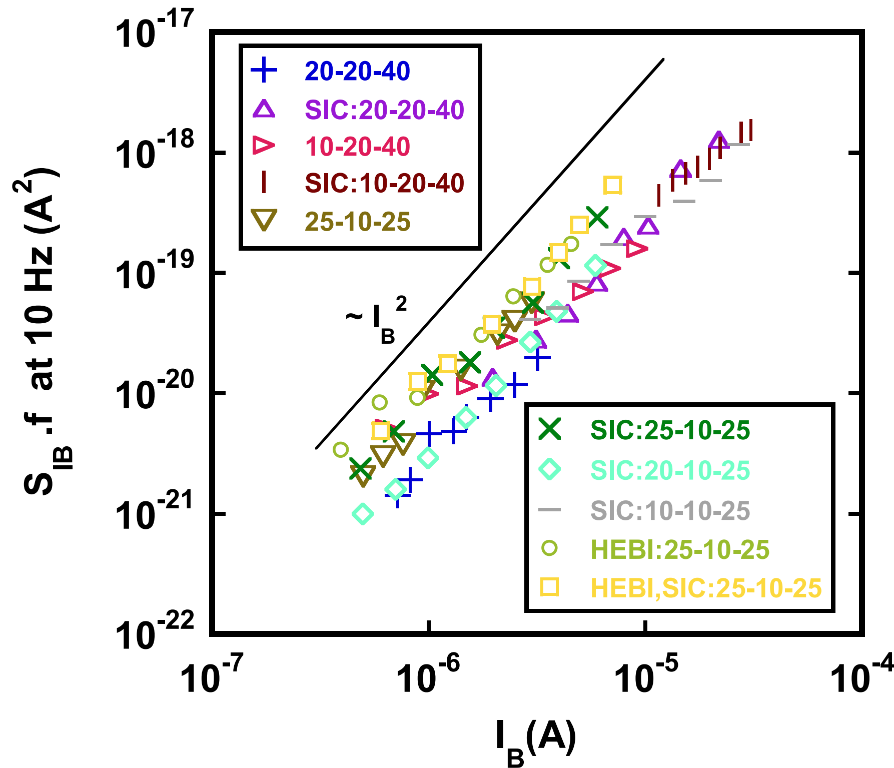
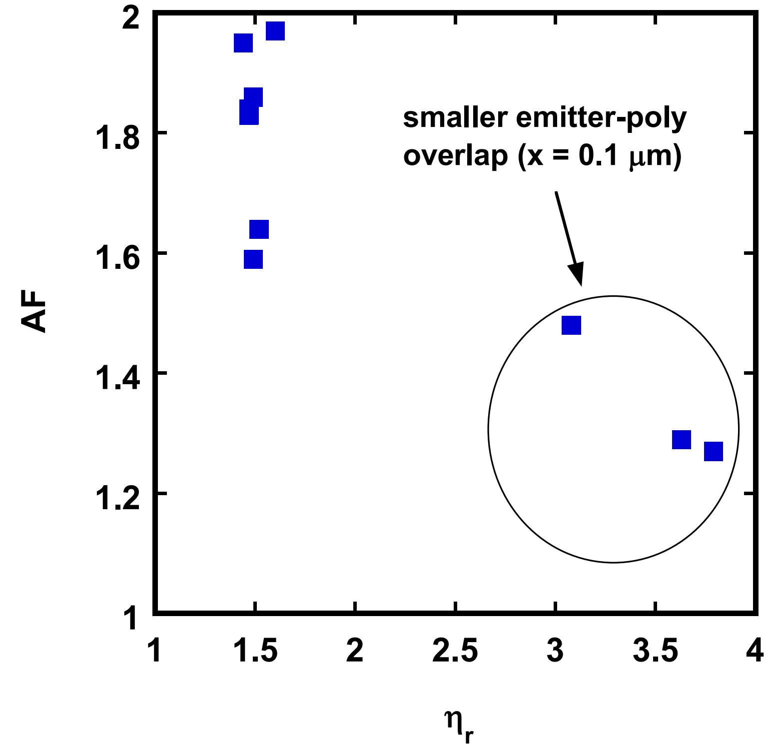
Physical origin of S_{IB}





- **All except smaller emitter-poly overlap → $\eta_r \leq 1.6$, AF≈2.**
- **Smaller emitter-poly overlap → $\eta_r > 3$, AF≈1.**

S_{IB} model

$AF \approx 2$

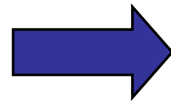
$$S_{I_B} = KF_1 \cdot I_B^2$$

$$KF_1 = \sum_{i}^{N_1} I_B^2 \frac{\tau_i}{1 + (2\pi f \tau_i)^2}$$

N_1 : Total number of traps in emitter-base junction.

τ_i : Characteristics time constant of ith trap.

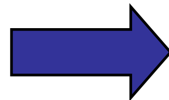
SRH g-r centers in E-B depletion region



Capture and emission of carriers

Perturbation in free carrier density

Continuous distribution of time constants

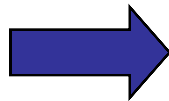


Superposition of Lorentzians

1/f noise

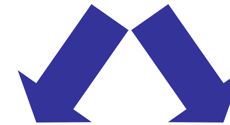
Noise from Surface recombination current

Smaller emitter-poly overlap



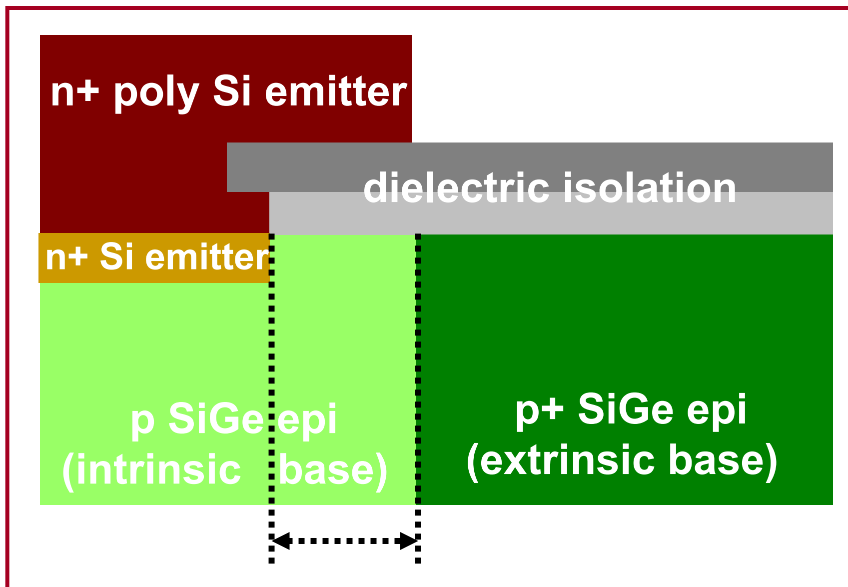
Extrinsic base moves closer to emitter perimeter

Two parallel BJTs

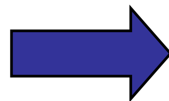


n+ emitter, p SiGe intrinsic base, collector

n+ emitter, p+ SiGe extrinsic base, collector



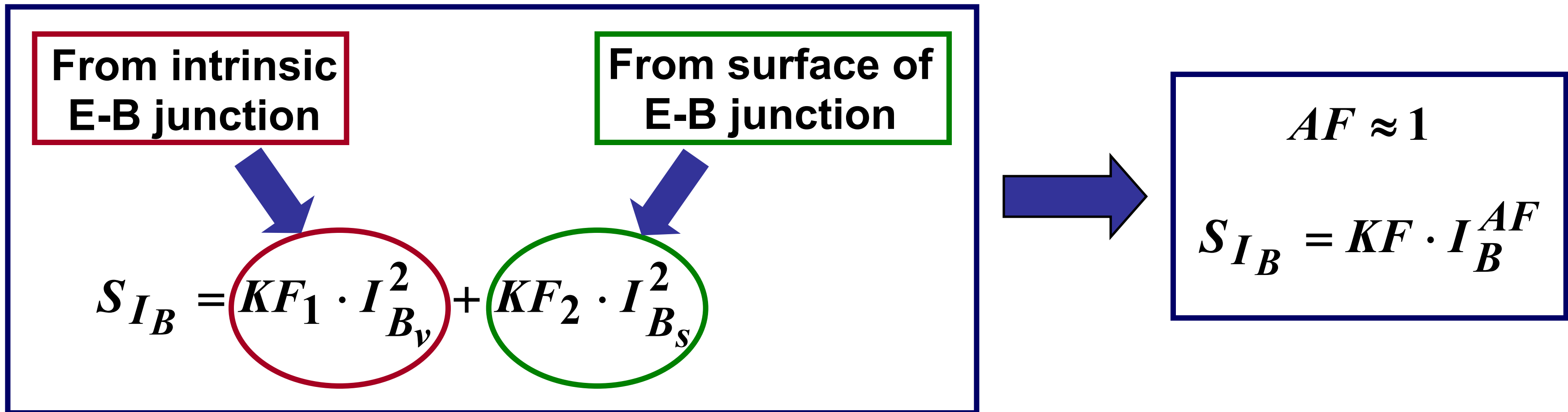
n+ emitter - p+ extrinsic base diode



Thin depletion region & high electric field

Recombination through trap assisted tunneling

S_{IB} model for smaller emitter-poly overlap



$$KF_2 = \frac{q^4 N_2 \lambda}{KTAC_{sc}^2 f}$$

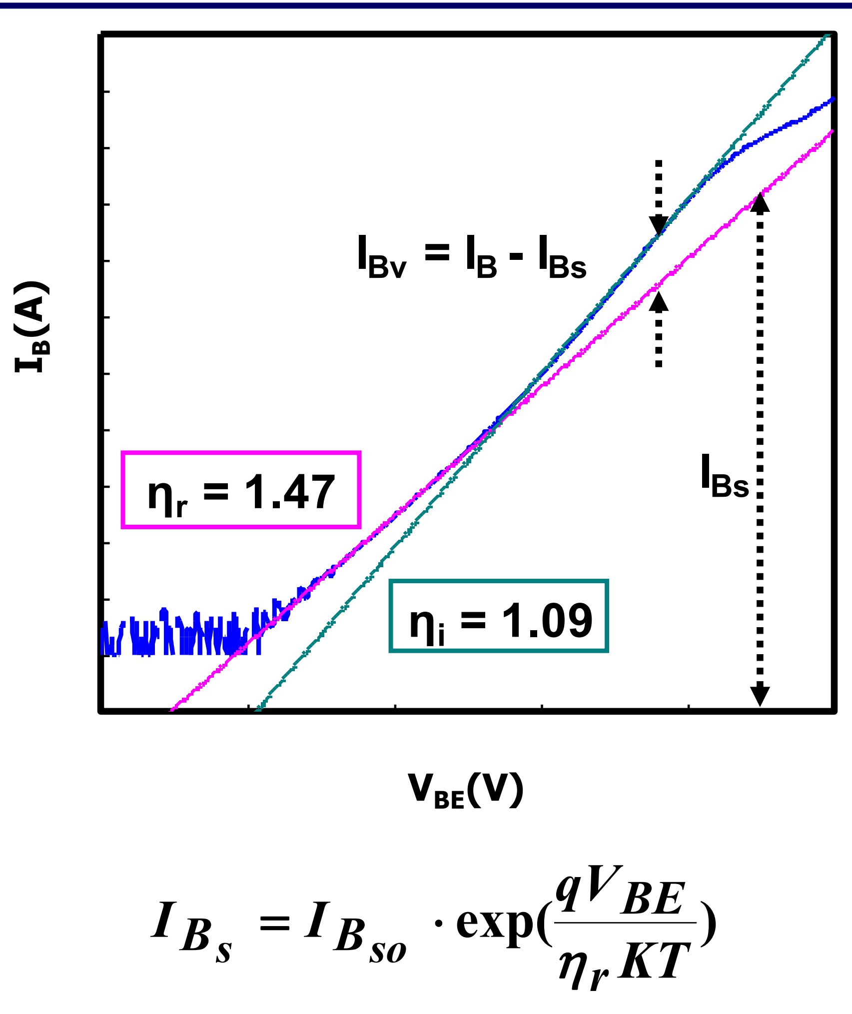
N_2 : Oxide slow state volume density.

λ : Attenuation tunneling distance.

A : Area of surface region.

C_{sc} : Surface capacitance per unit area.

Separation of S_{I_B} components



$$I_{B_s} = I_{B_{so}} \cdot \exp\left(\frac{qV_{BE}}{\eta_r KT}\right)$$

$$S_{I_B} = KF_1 \cdot I_{B_v}^2 + KF_2 \cdot I_{B_s}^2$$

$$\frac{S_{I_B}}{I_{B_s}^2} = KF_1 \frac{I_{B_v}^2}{I_{B_s}^2} + KF_2$$

N_2 = 9.65x10[15] ~ 3.08x10[16] /eV/cm[3].

Published values = 10[17] ~ 10[18] /ev/cm[3].

Uncertainties in λ and C_{sc} .

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Conclusion

Polysilicon emitter bipolar transistors:

- **The base current fluctuations dominate at relatively high external base resistance values.**
- **Collector current fluctuations contribute when the external base resistance becomes comparable to or less than the input resistance.**
- **Fluctuations caused by the internal emitter resistance take over for high currents with small base resistance.**
- **From the dependence of noise magnitude on the geometry and temperature, fluctuations in the non-ideal base current was neglected.**

Conclusion (cont.)

- S_{IB} originates from diffusion fluctuations of minority carriers in poly and monosilicon emitter, and tunneling fluctuations of minority carriers at IFO; S_{IC} from diffusion and number fluctuations of minority carriers in base, and S_{Vre} from tunneling fluctuations of majority carrier at IFO.
- Diffusion fluctuations dominate over the tunneling fluctuations for larger devices; tunneling fluctuations dominate over diffusion fluctuations for the smaller ones.
- IFO increases the current gain significantly in NPN; both tunneling and diffusion fluctuations contribute.
- No significant improvement with increasing IFO thickness in PNP; diffusion fluctuations dominant.

Conclusion (cont.)

SiGe heterojunction bipolar transistors:

- Selectively implanted collector causes higher current gain for wider range of bias; no noise degradation.
- No significant effect of SiGe epi-SiGe poly interface and higher extrinsic base implant.
- Severe impact of smaller emitter-poly overlap:
  - increases non-ideality of the base current; trap assisted tunneling current due to parasitic BJT.
  - g-r noise at lower bias currents.
  - At higher bias currents, fluctuations from trap assisted tunneling current contribute.
- For all transistors except smaller emitter poly overlap, noise originates from intrinsic E-B junction.

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  - Texas Instruments Inc.
  - National Semiconductor Corporation
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  - Bigang Min, Siva P. Devireddy, Shadi Dayeh, Enhai Zhao